

The path to large scale quantum computing based on CMOS technology

Maud Vinet, CEO
Siquance

VLSI technology

Advanced CMOS integration
IC design and architecture

Quantum engineering

Coherent control of electron
spins in semiconductors

CMOS Device physics

Spin and charge properties
of Si CMOS devices



20 years

Quantum computing value creation is huge



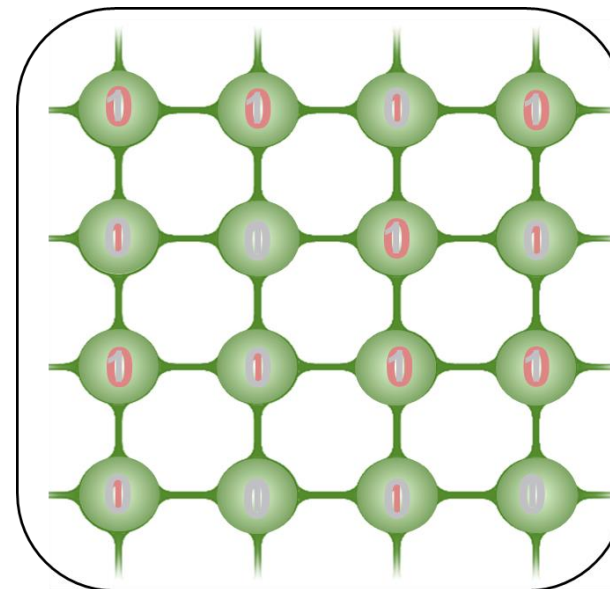
¹ Based on data taken from Langione et al., "Where Will Quantum computers Create Value and When?" Boston Consulting Group, May 2019. ² Hazan et al., "The Next Tech Revolution: Quantum Computing." McKinsey & Company, March 2020. What Happens When 'If' Turns to 'When' in Quantum Computing? Jean-François Bobier, Matt Langione, Edward Tao, and Antoine Gourévitch, July 2021

Living with errors

› Millions of errorless operations

Quantum Error Correction protocols

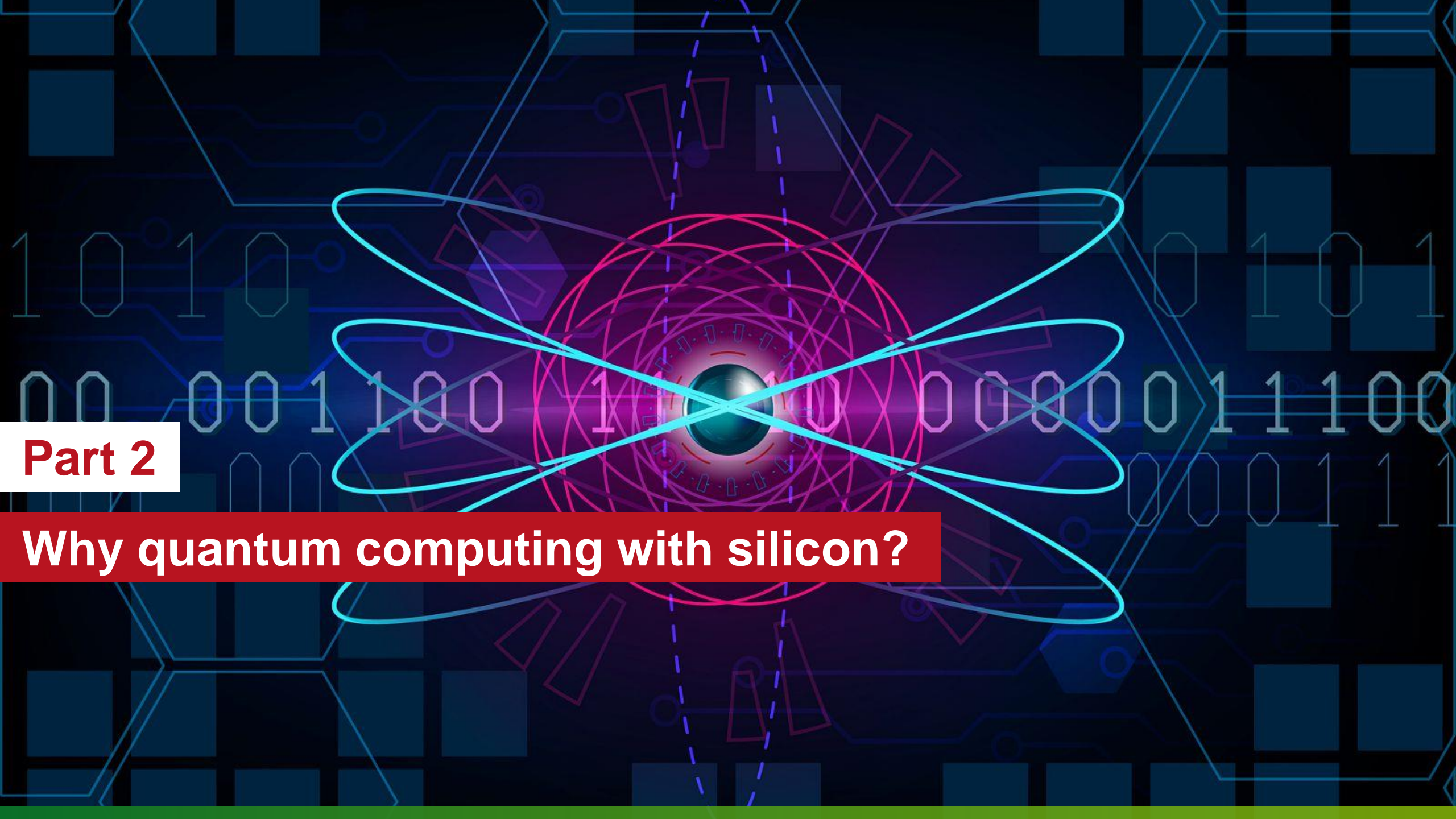
› More than **100 000** of physical qubits in 2D arrays



1 errorless logical qubit
> 1000 physical qubits

Part 2

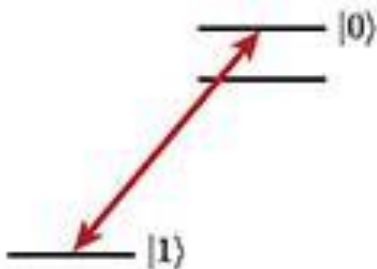
Why quantum computing with silicon?



Many qubits experimental platforms

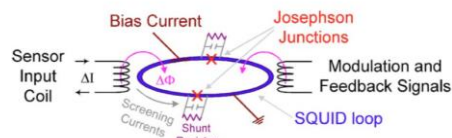
Quantum information

atom



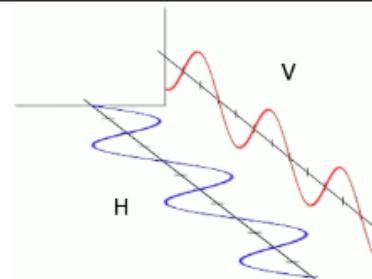
Atomic energy level

superconductors



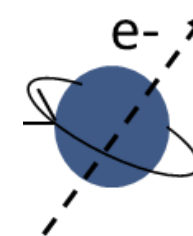
Phase or energy in a current loop

photons



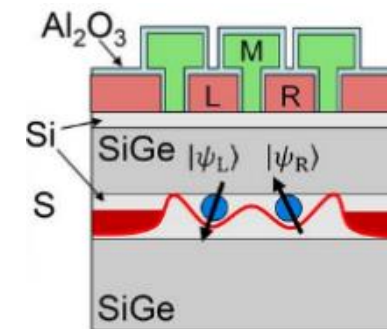
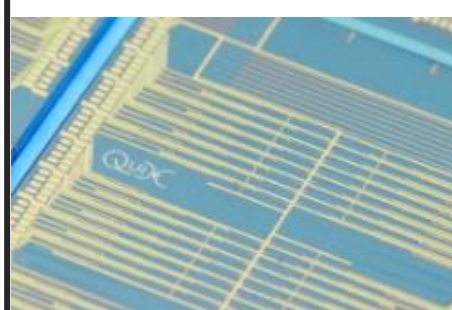
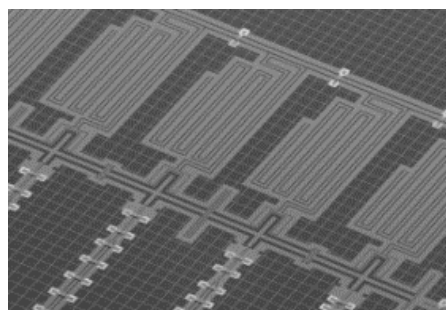
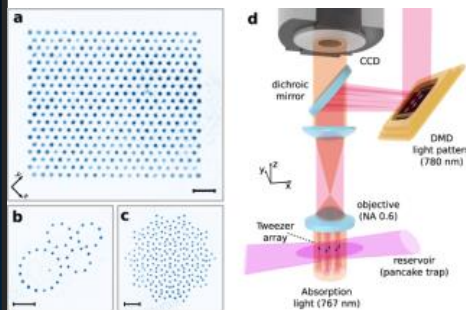
Photon polarisation (or other properties)

Si qubits



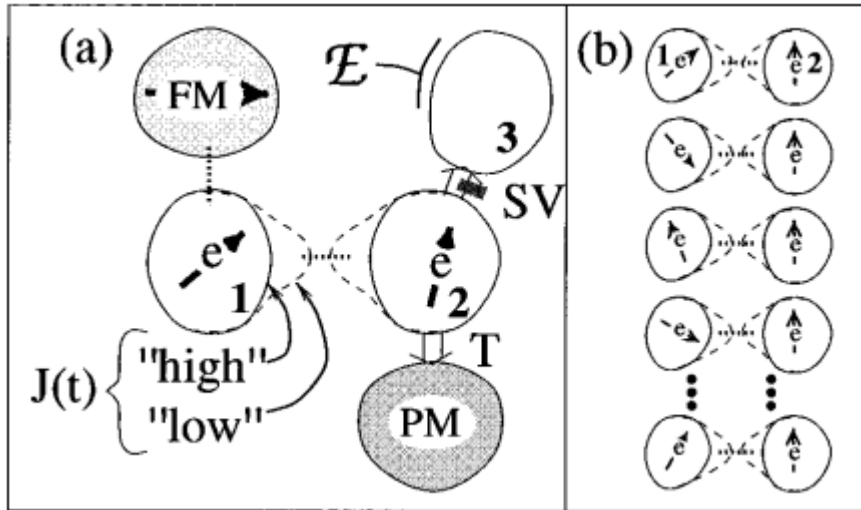
Spin degree of freedom of a charge

Physical aspect

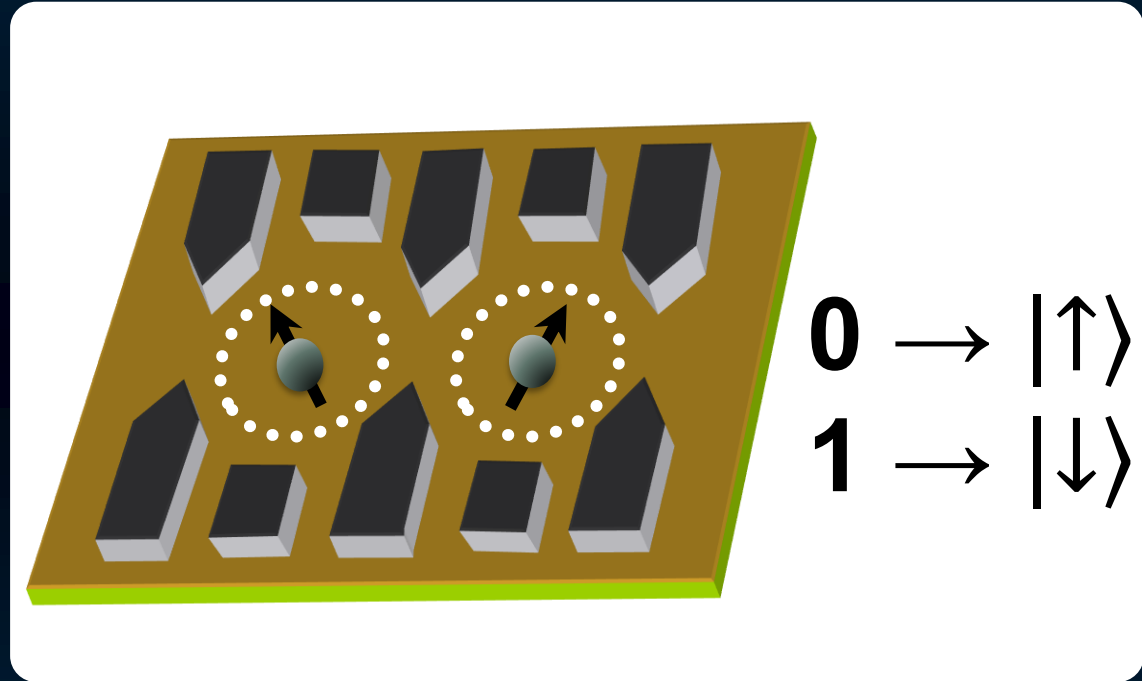


Silicon spin qubits

› 1998 theoretical concept



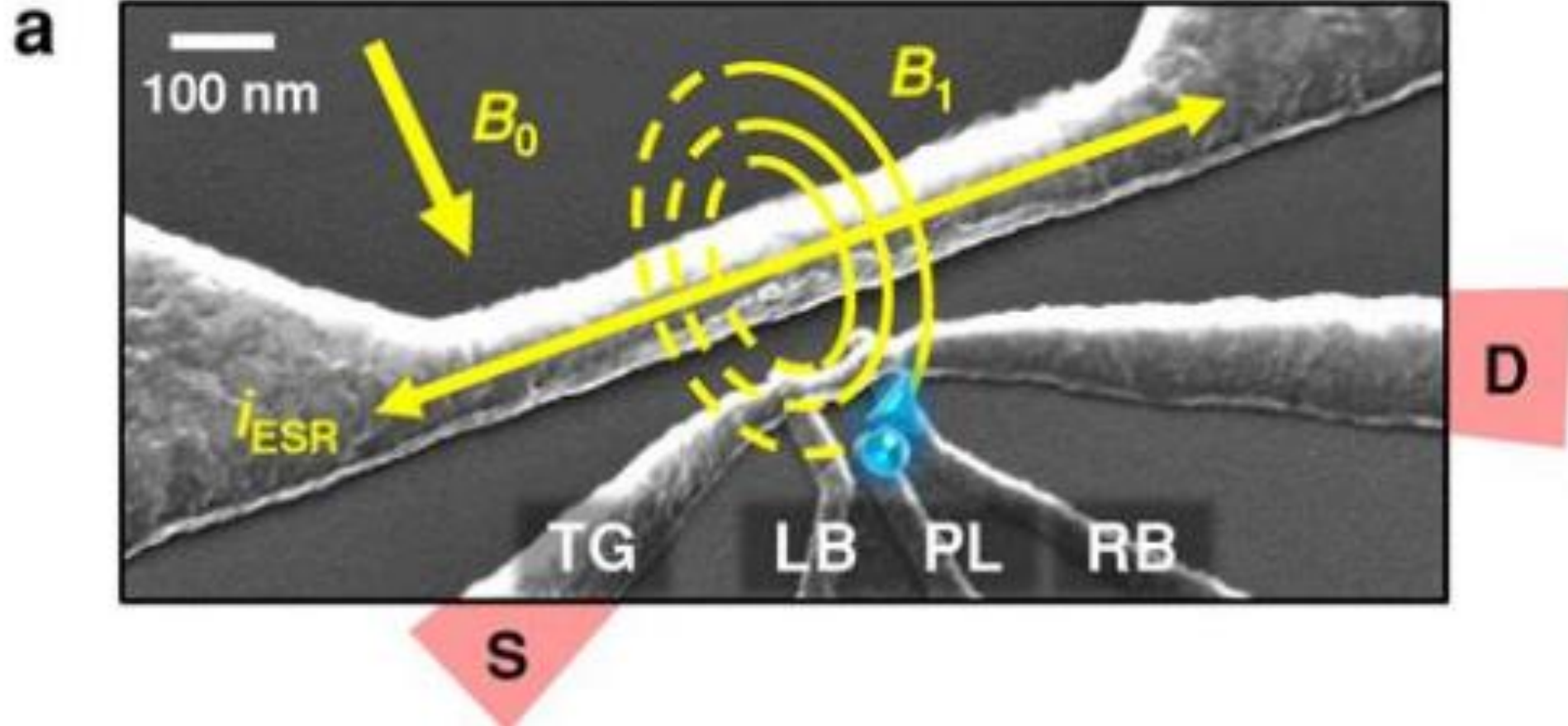
Loss, D. and DiVincenzo, D. Quantum computation with quantum dots, *Phys. Rev. A* 57, 120 (1998)



Spin degree of freedom of an electron
Gate defined quantum dots

Silicon spin qubits

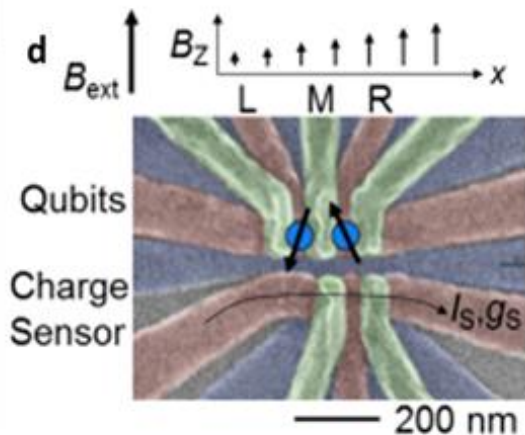
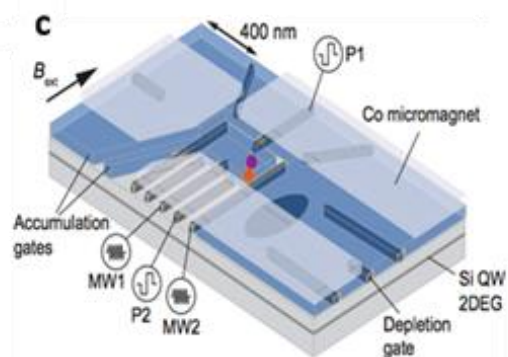
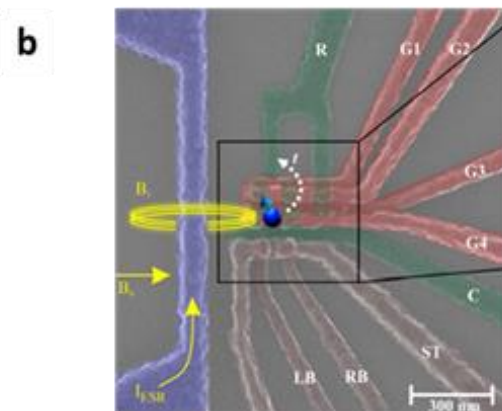
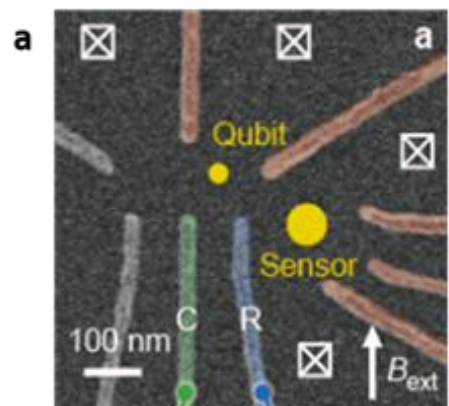
› 2012: first experimental demonstration



Pla, J., Tan, K., Dehollain, J. et al. A single-atom electron spin qubit in silicon. Nature 489, 541–545 (2012).

Early academics demonstrations

› Many gates planar designs



Si MOS
SiGe/Se

› RIKEN (a) UNSW (b) Delft (c) and Princetown (d)

Figures of merit – State of the art

Size*
1qubit fidelity
2qubit fidelity
Speed**
Variability
T° of operation
Entangled qubits

* Estimation taking into account all the quantum functionalities (read out, control and initialization)

** Speed of the limiting operation between read out and measurement

Figures of merit – State of the art

	Superconductor	Si spin qubit	Trapped ion	Photon
Size*	(100 μ m) ²	(100nm) ²	(1mm) ²	~(100 μ m) ²
1qubit fidelity	99.96%	99.93%	99.98%	
2qubit fidelity	~99.3%	>99%	99.9%	50% (measurement) 98% (gates)
Speed**	12-400 ns	~1 μ s	100 μ s	1 ms
Variability	3%	0.1%-0.5%	0.01%	0.5%
T° of operation	15mK	1K	10K	4K/10K
Entangled qubits	433 (IBM)	3 (TU) (6 - QuTech)	32 (IonQ)	70 (Pan-China)

* Estimation taking into account all the quantum functionalities (read out, control and initialization)

** Speed of the limiting operation between read out and measurement

Figures of merit – State of the art

	Superconductor	Si spin qubit
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Variability	3%	0.1%-0.5%
T° of operation	15mK	1K
Entangled qubits	433 (IBM)	3 (TU) (6 - QuTech)

✓ Size

up to 100 000 per mm²

✓ Quality

above error correction threshold

✓ Speed

1s for millions of operations - compatible with competitive run time

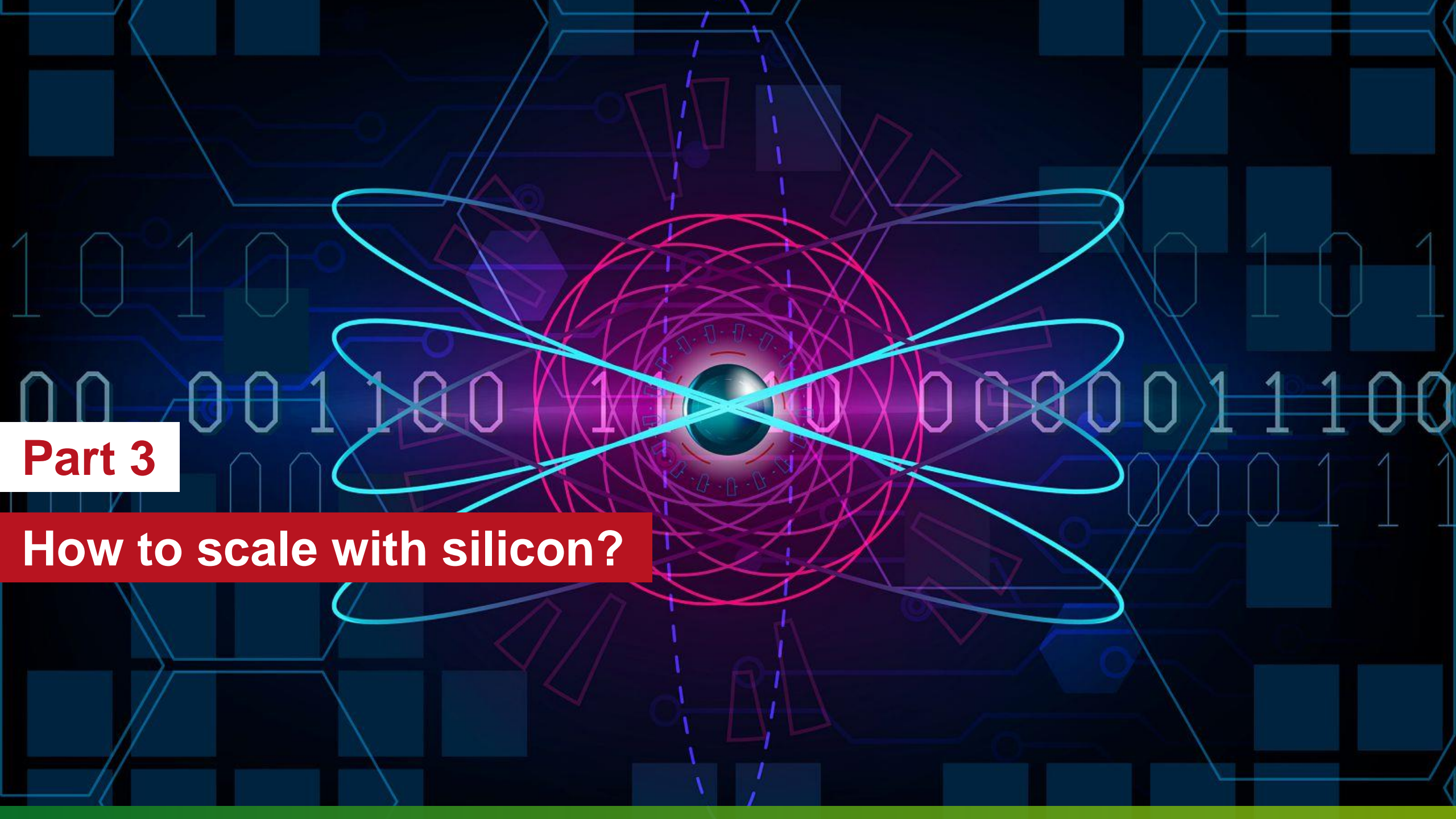
Silicon is a very promising candidate for scaling

* Estimation taking into account all the quantum functionalities (read out, control and initialization)

** Speed of the limiting operation between read out and measurement

Part 3

How to scale with silicon?

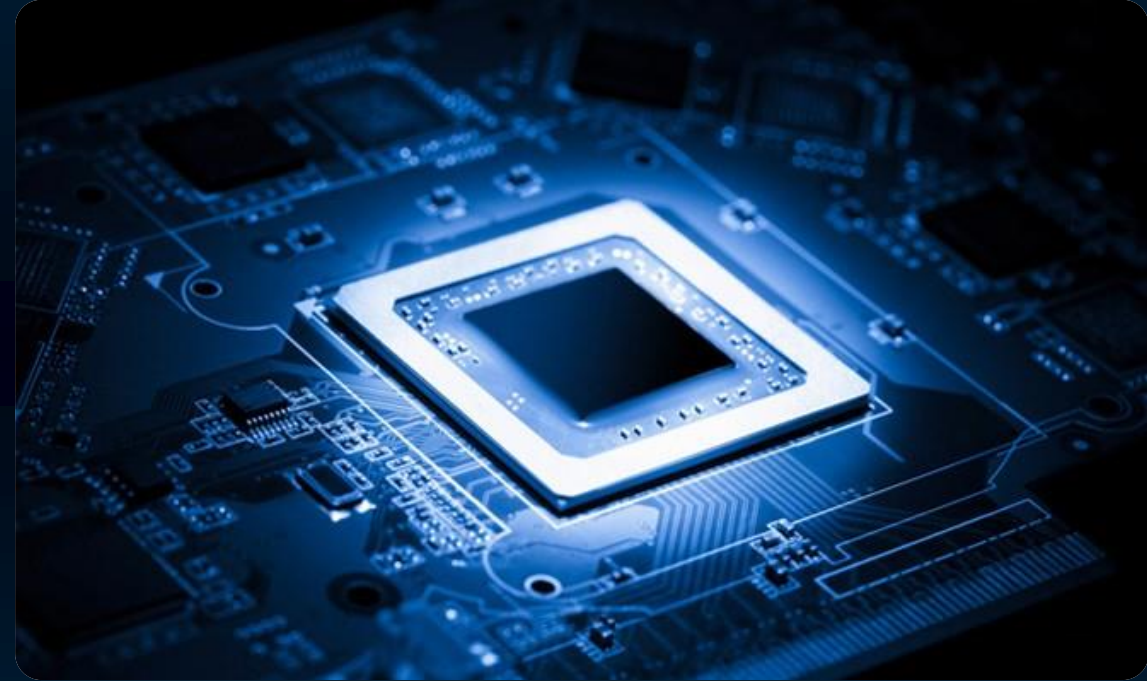


Semiconductor industry power

Potential to fabricate billions of devices



Integrated circuits



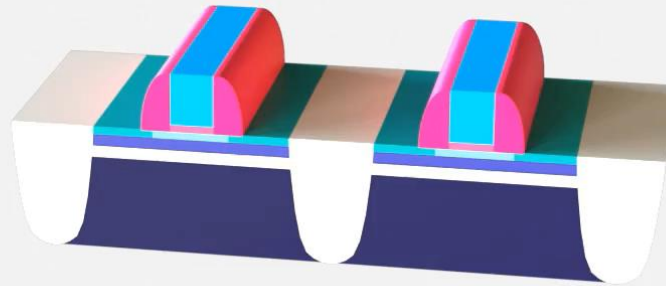
Potential to efficiently control and program millions of qubits

Fastest path to leverage semiconductor industry potential

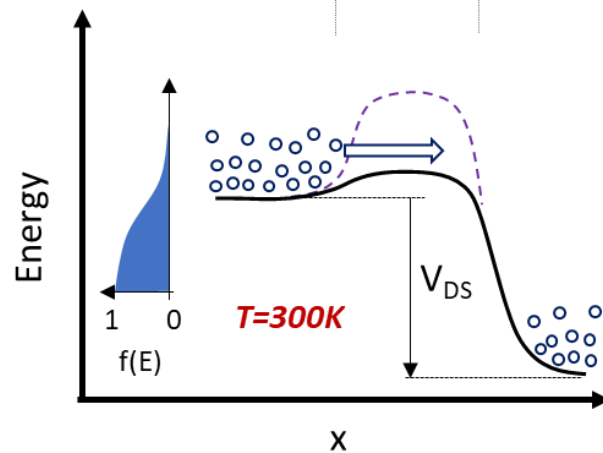
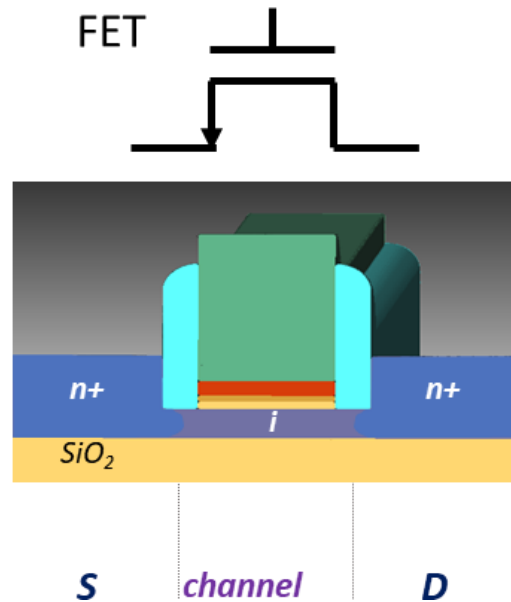
- › Transform a transistor into a good qubit

Fastest path to leverage semiconductor industry potential

› Transform a transistor into a good qubit



Silicon spin qubits, from transistors...



At room temperature:

- › Carriers have significant thermal energy
- › Diffusion over the S/channel barrier when V_G is turned ON
- › Continuous flow of carriers accelerated by large V_{DS}

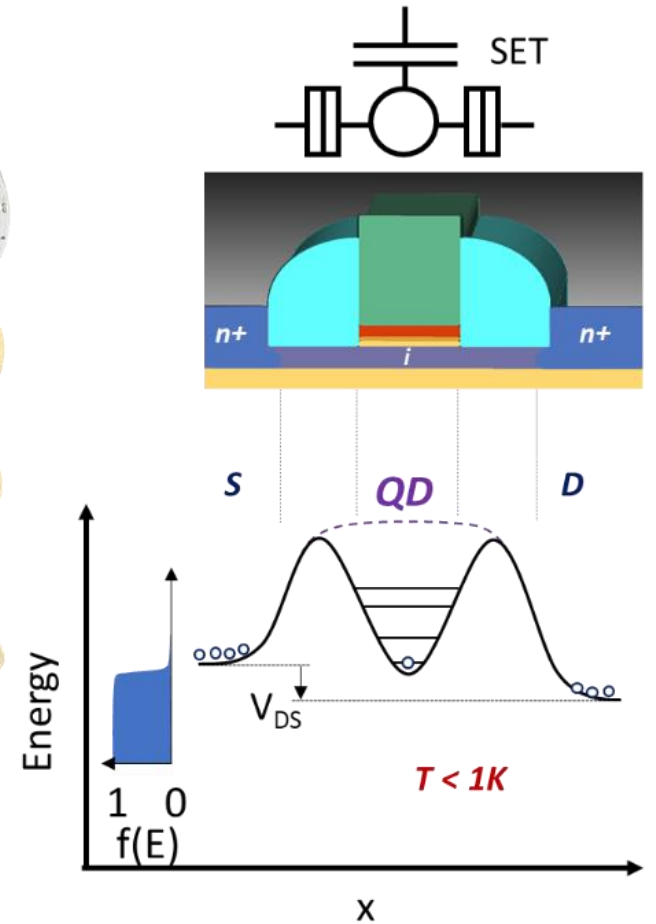
...To quantum dots

At low temperature:

- › Formation of a well between two barriers
- › Carriers have no thermal energy and have to tunnel through
- › Energy states are quantized in the well
- › Small VDS to scan precisely the resolved quantum states



$T = 0.01 \text{ K}$



And to qubits

- › Utilize magnetic field to lift degeneracy between spin up and spin down

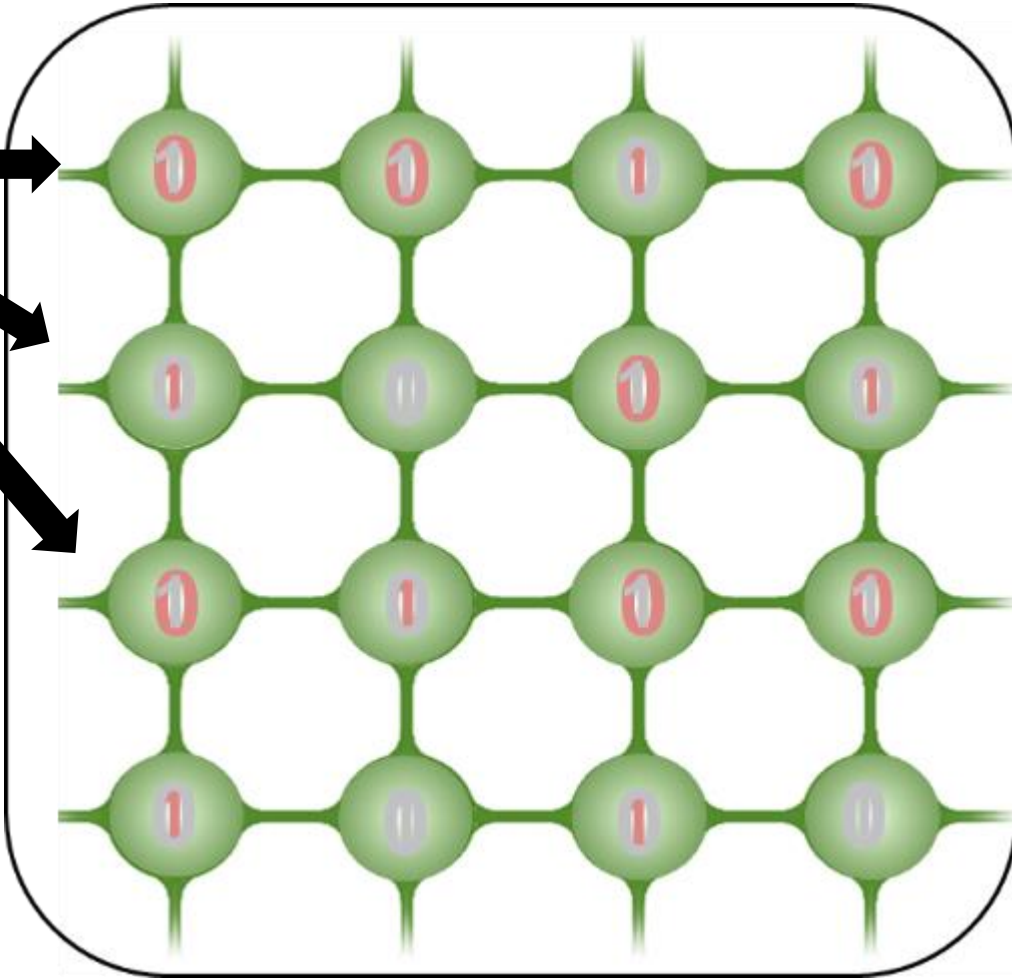
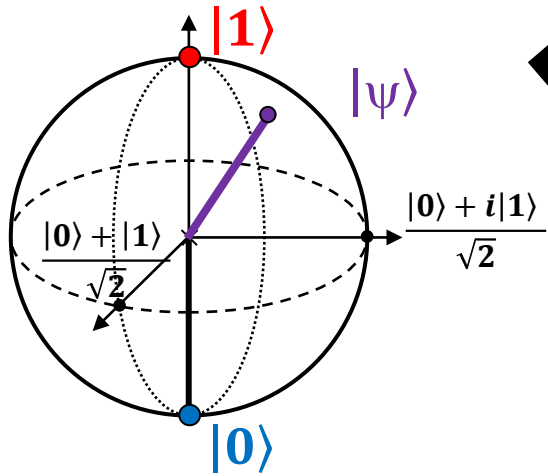
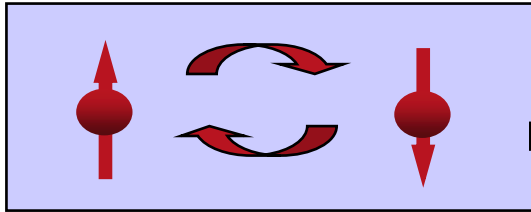
Static magnetic field B ,
two-level spin qubit



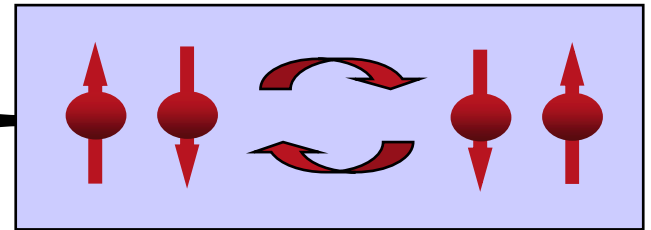
What is needed to implement algorithms now?

› Basic operations

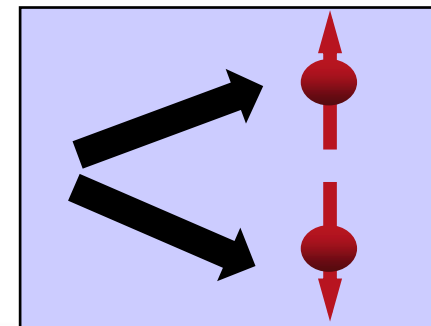
One-qubit gate



Two-qubit gate

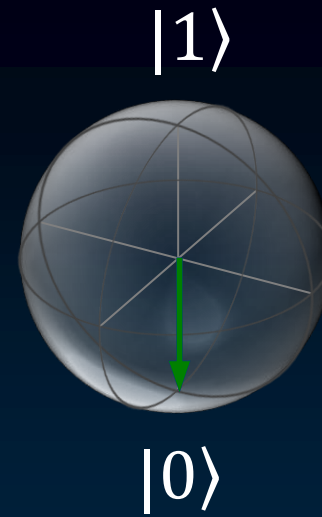
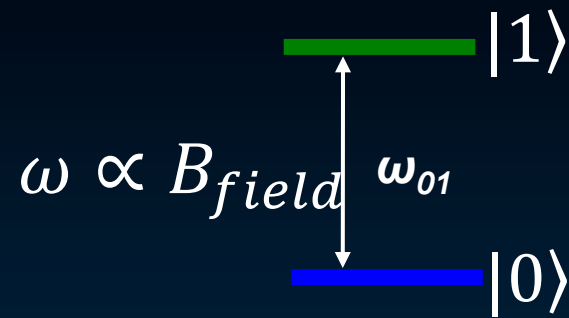
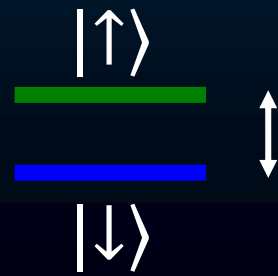


Read-out gate

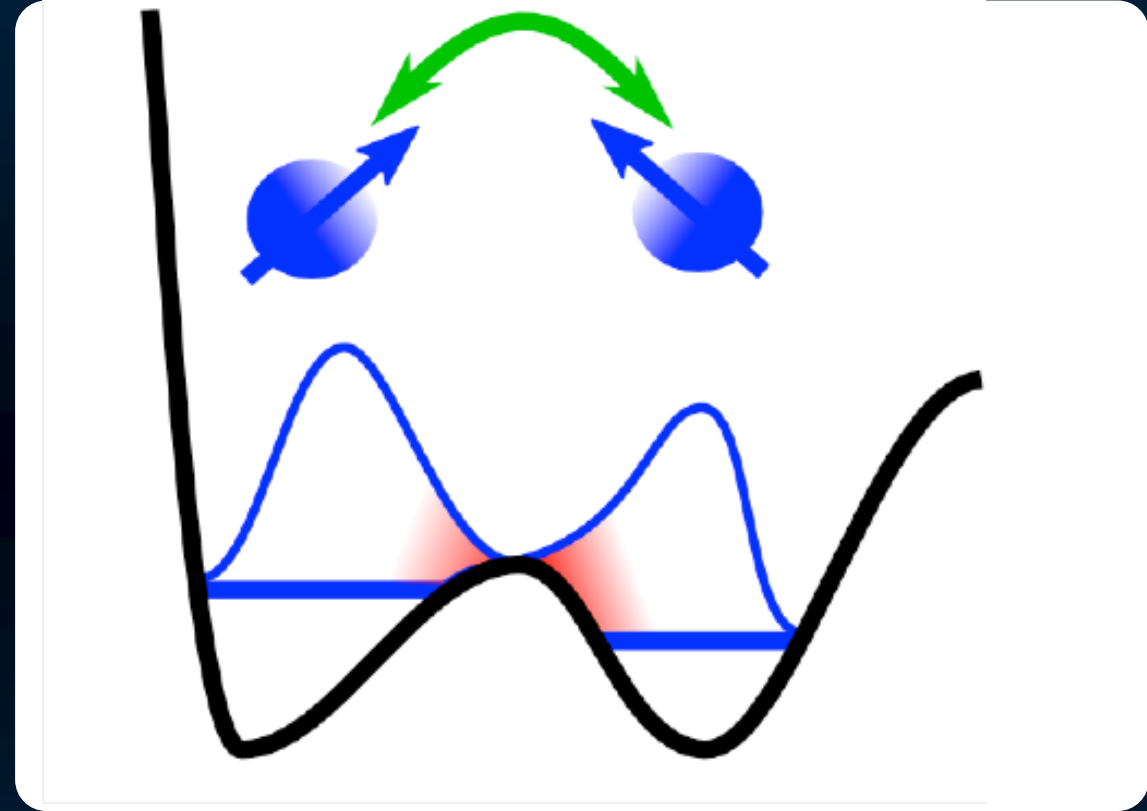
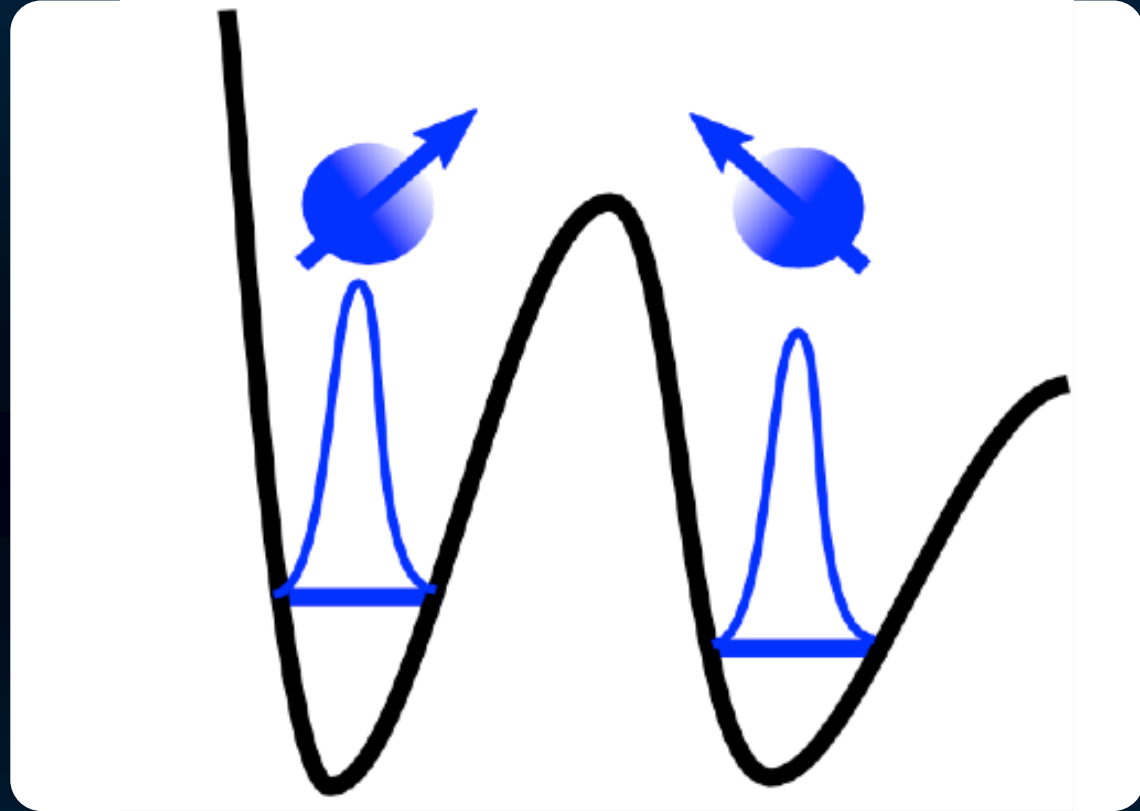


Single qubit gate, single qubit rotation

Static magnetic field B ,
two-level spin qubit:



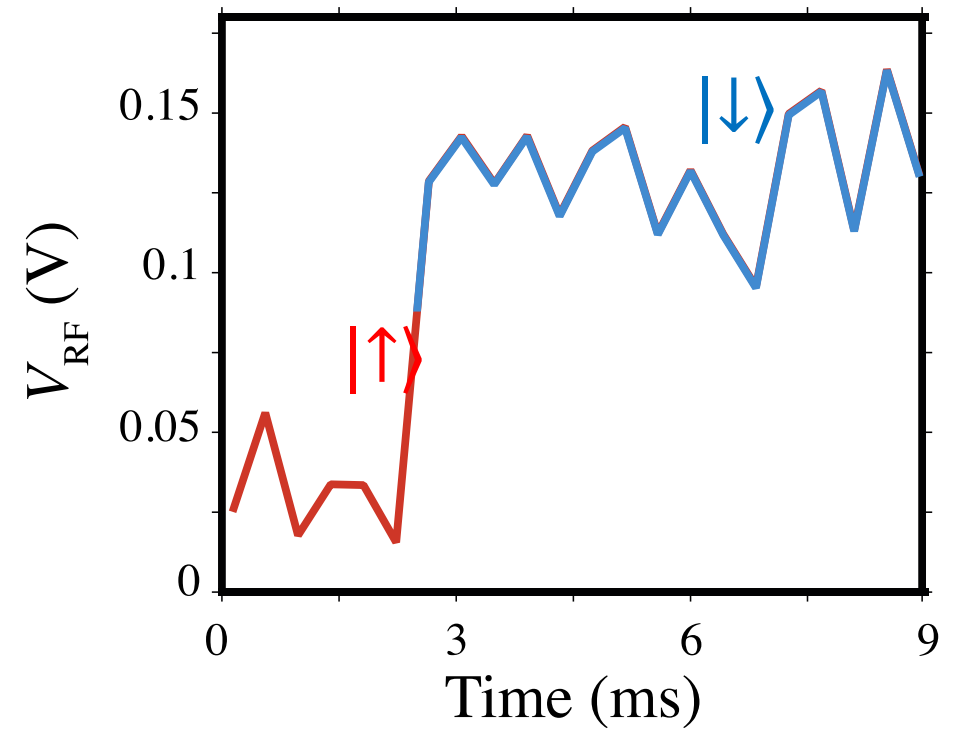
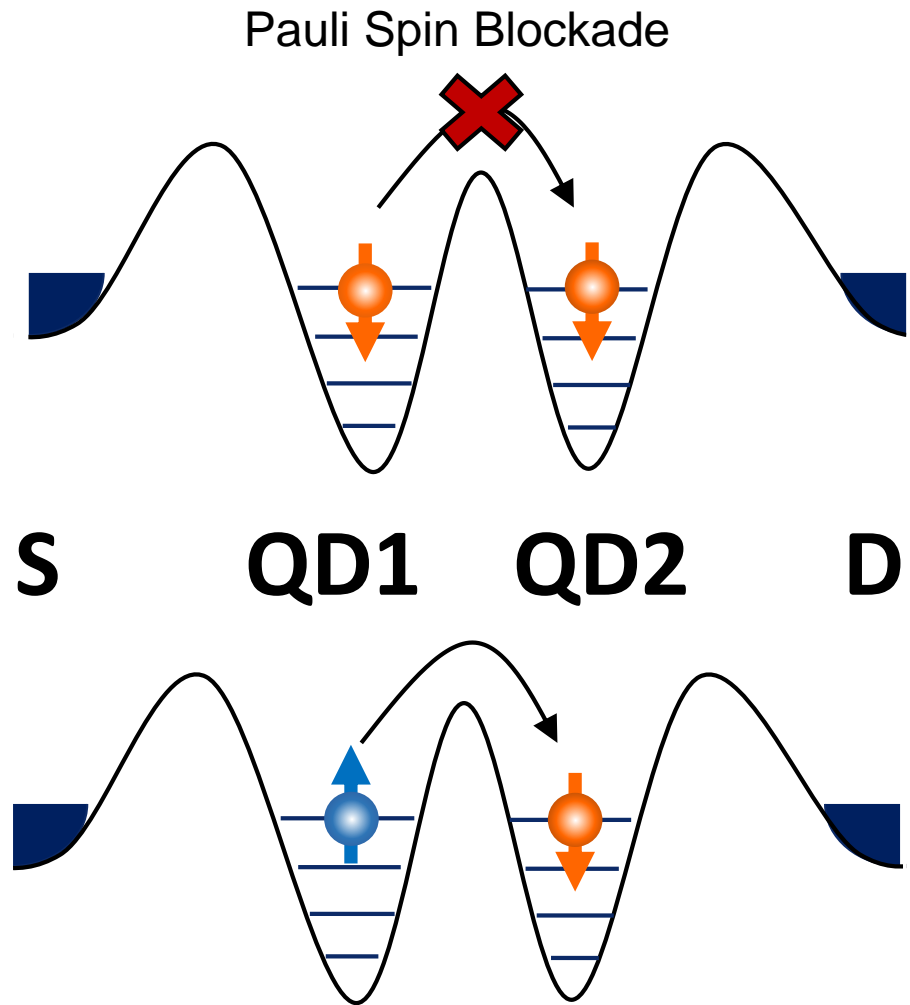
Two qubit gates by tunnel barrier lowering between adjacent dots



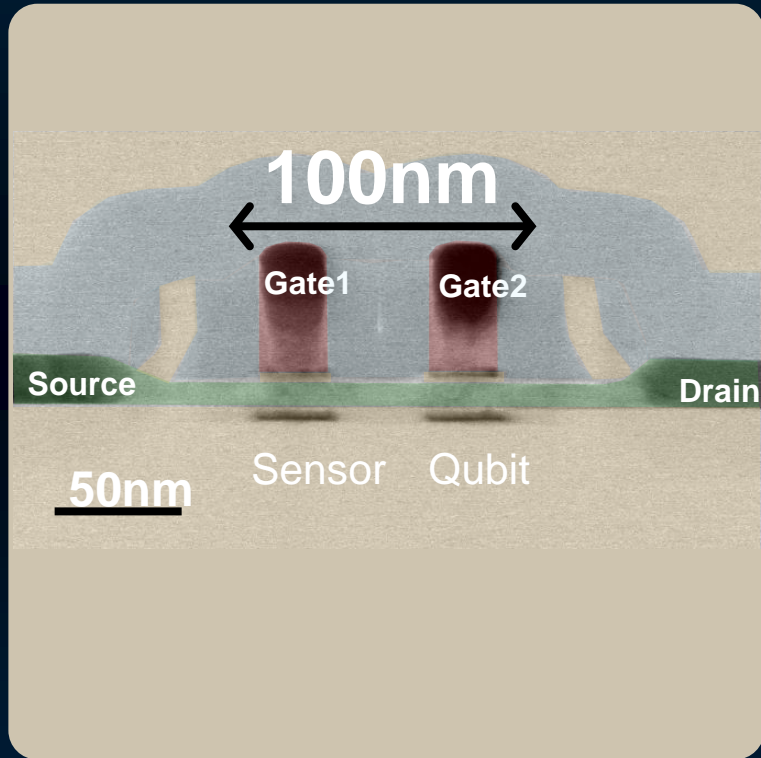
Spin exchange interaction

How to read out the value of the spin?

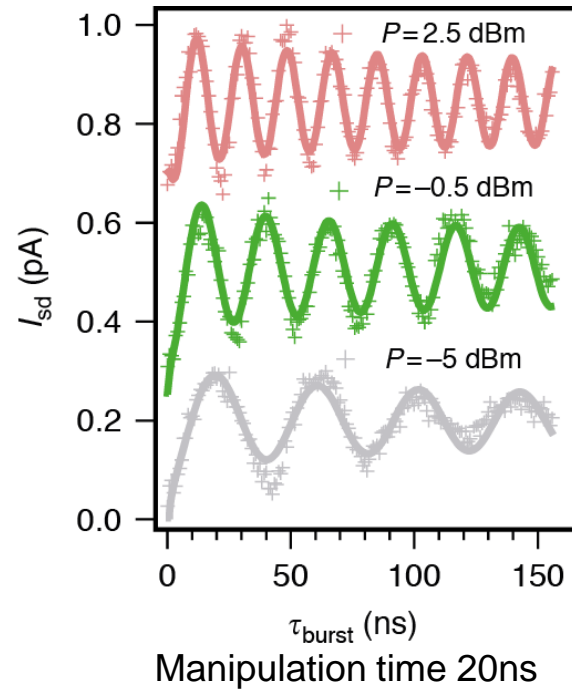
› Spin to charge conversion



2016 first transistor derived into a qubit

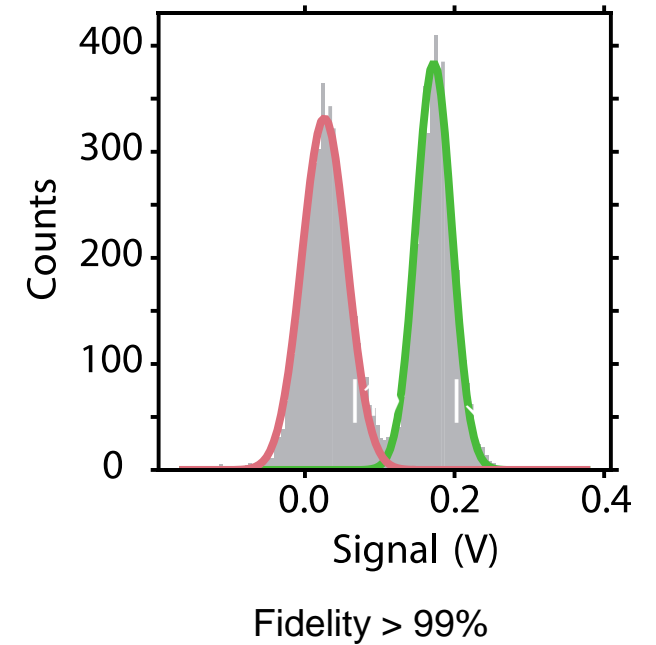


Single qubit gate



R. Maurand, Nat. Comm. (2016)

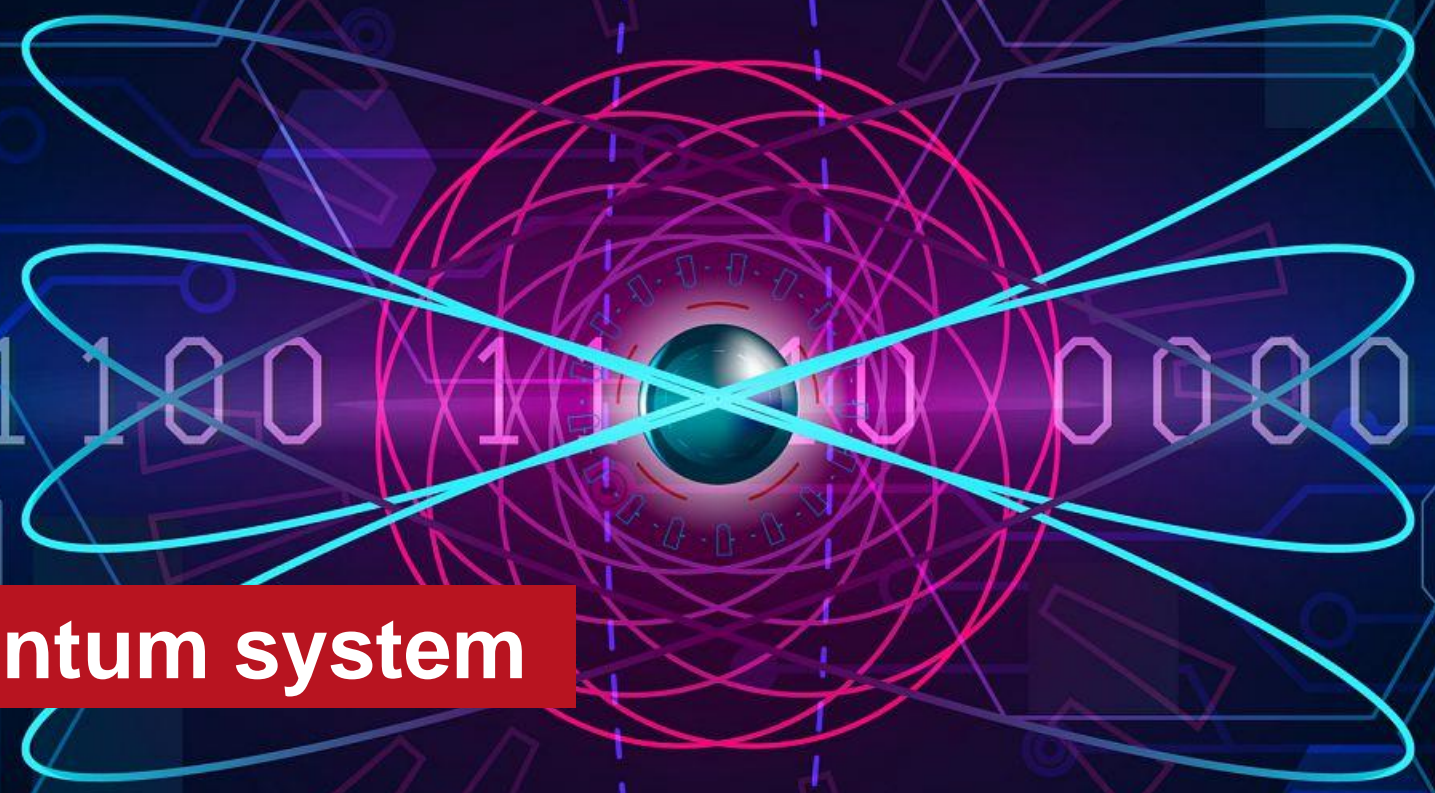
High fidelity RF scalable spin read-out



M. Urdampilleta, Nat. Nanotech (2019)

Part 4

Si based quantum system



Silicon based quantum computer

Cryo control electronics

- Low power fast electronics

Cryo wires and connectors

- Need customized solutions.

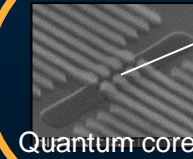
Cryostats

- High power ~1W @ 1K

Room T° electronics

- AWG

Substrates



Device Technology

Core FDSOI technology

- Dedicated DRM
- Dedicated material expertise

Fully enabled quantum μ Processor

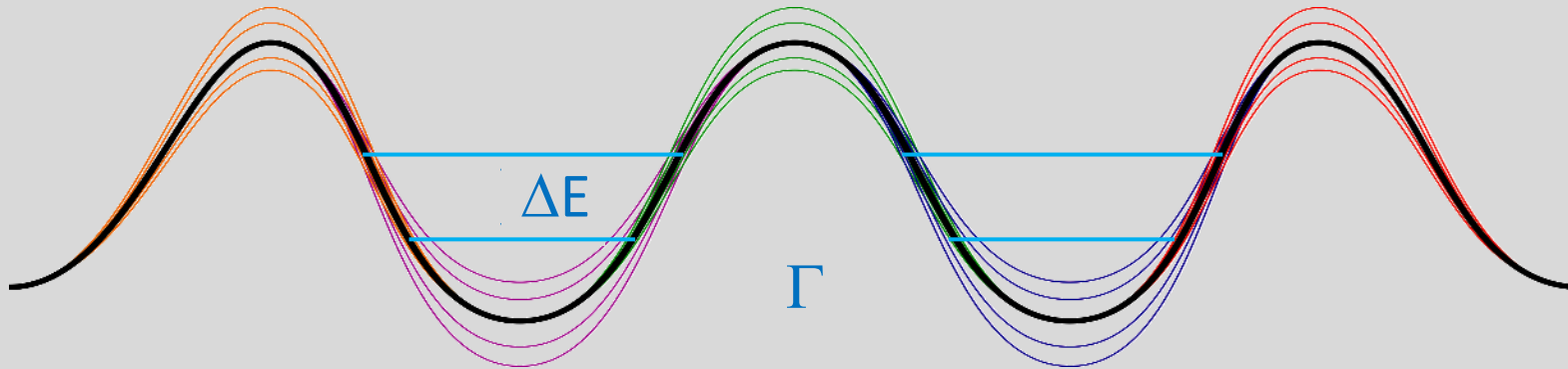
Packaging

- 3D interposers
- Cryopackage

Firmware layer



Application Layer or Work Load



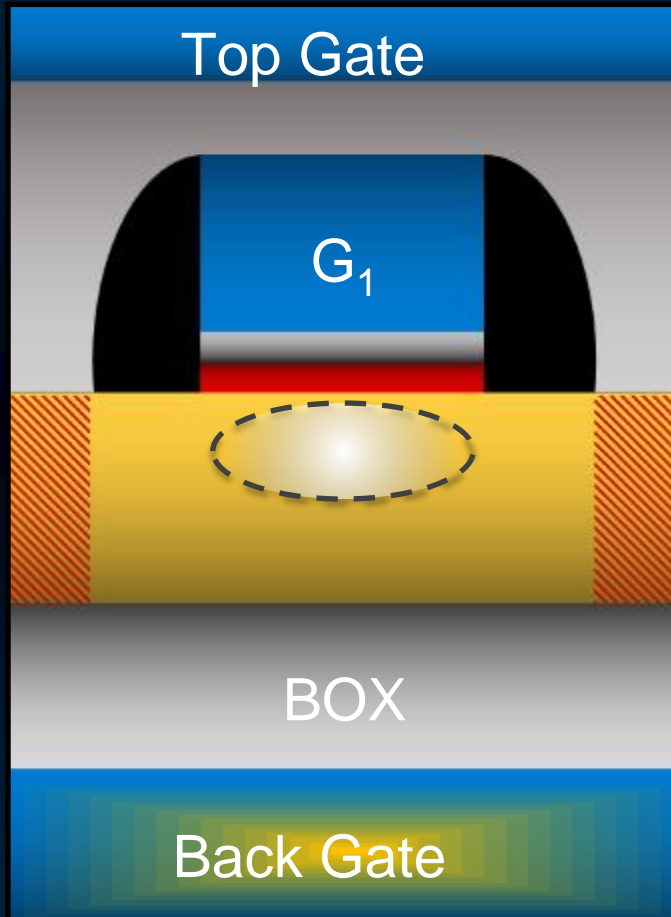
Well defined (electrostatically controlled) quantum wells separated by tunnel barriers

Quantum Interface

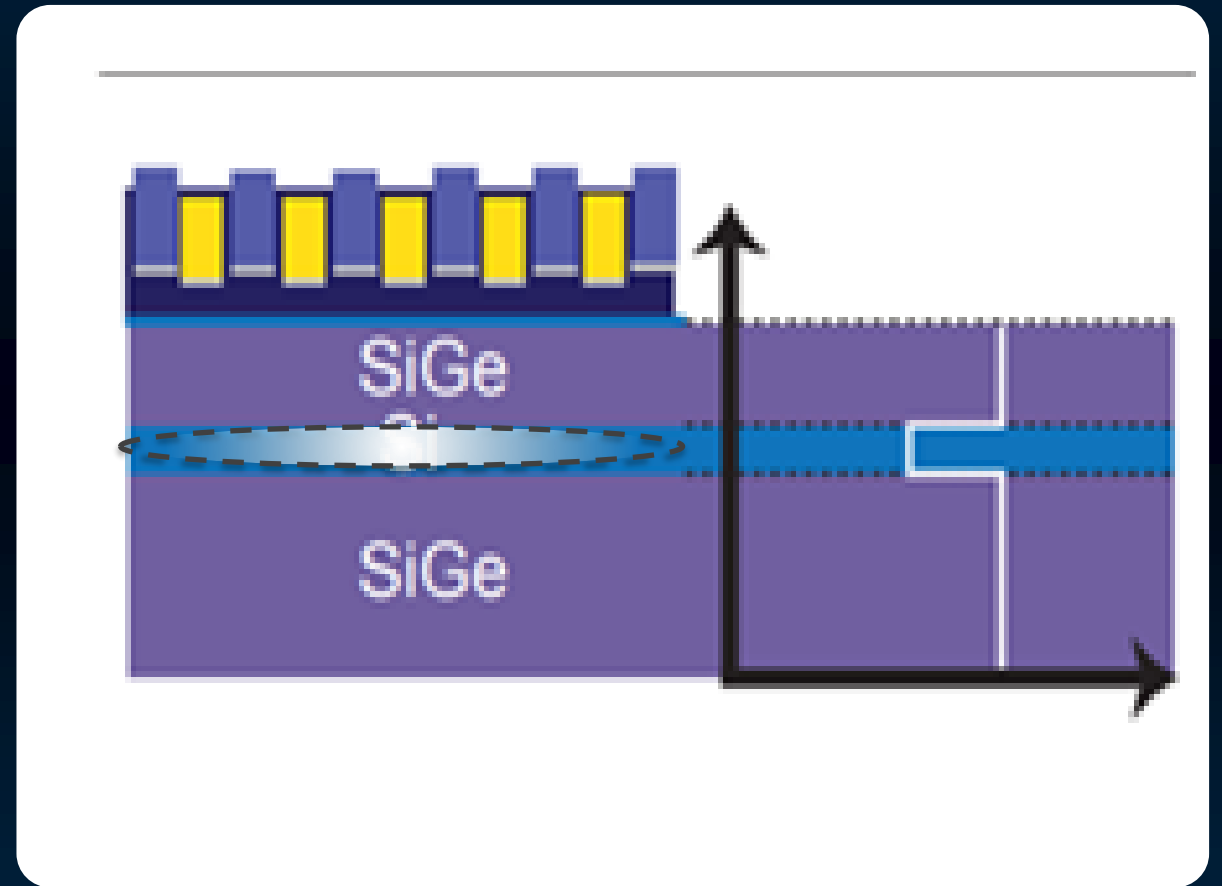
Quantum Chip

Moving away from interfaces

› Two options



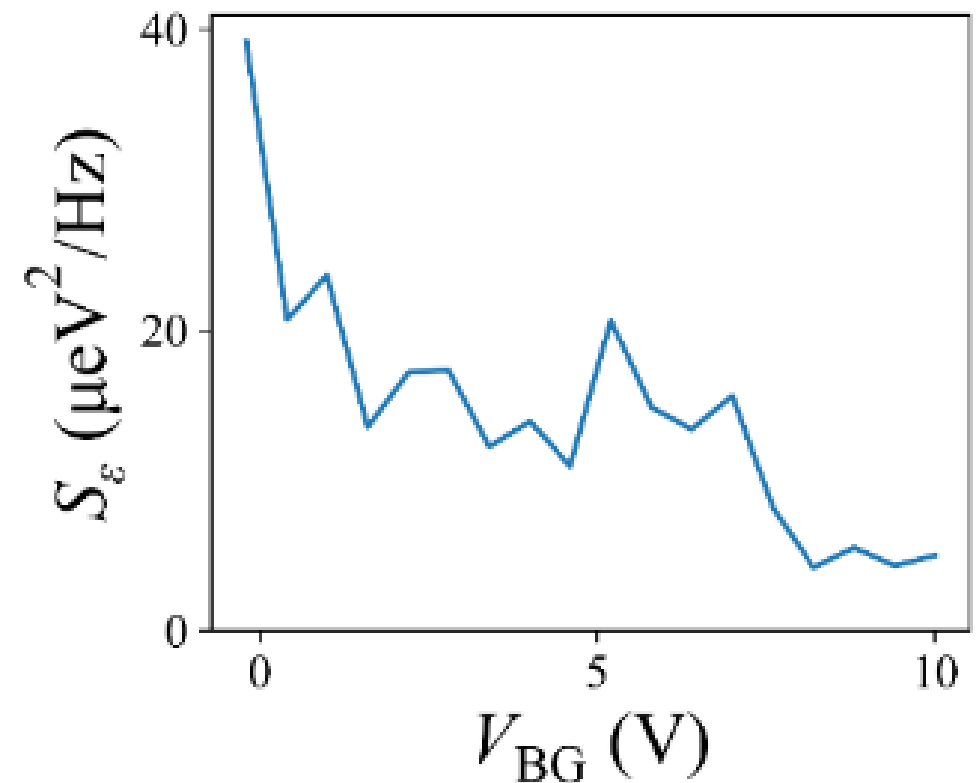
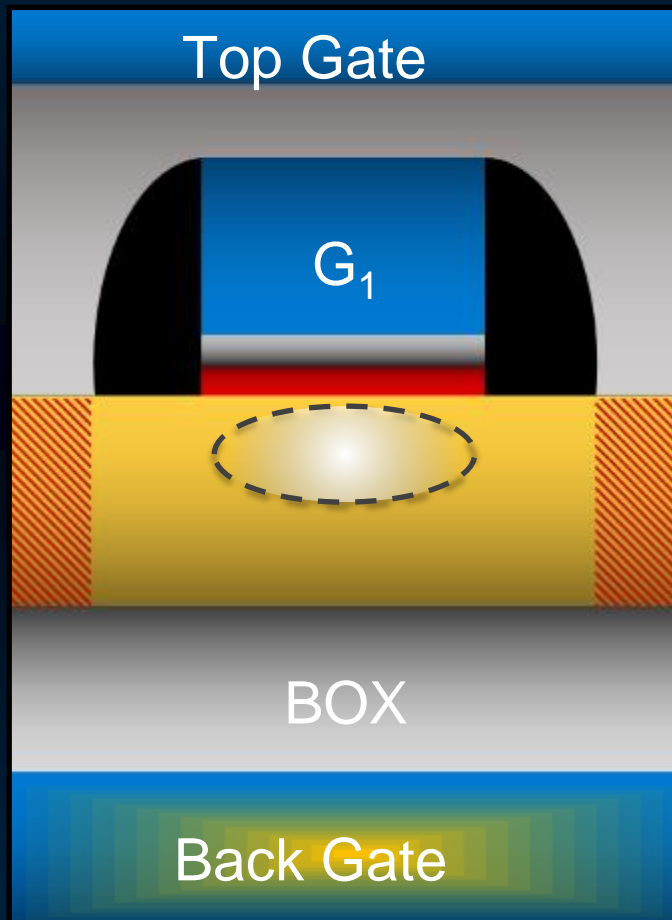
SOI



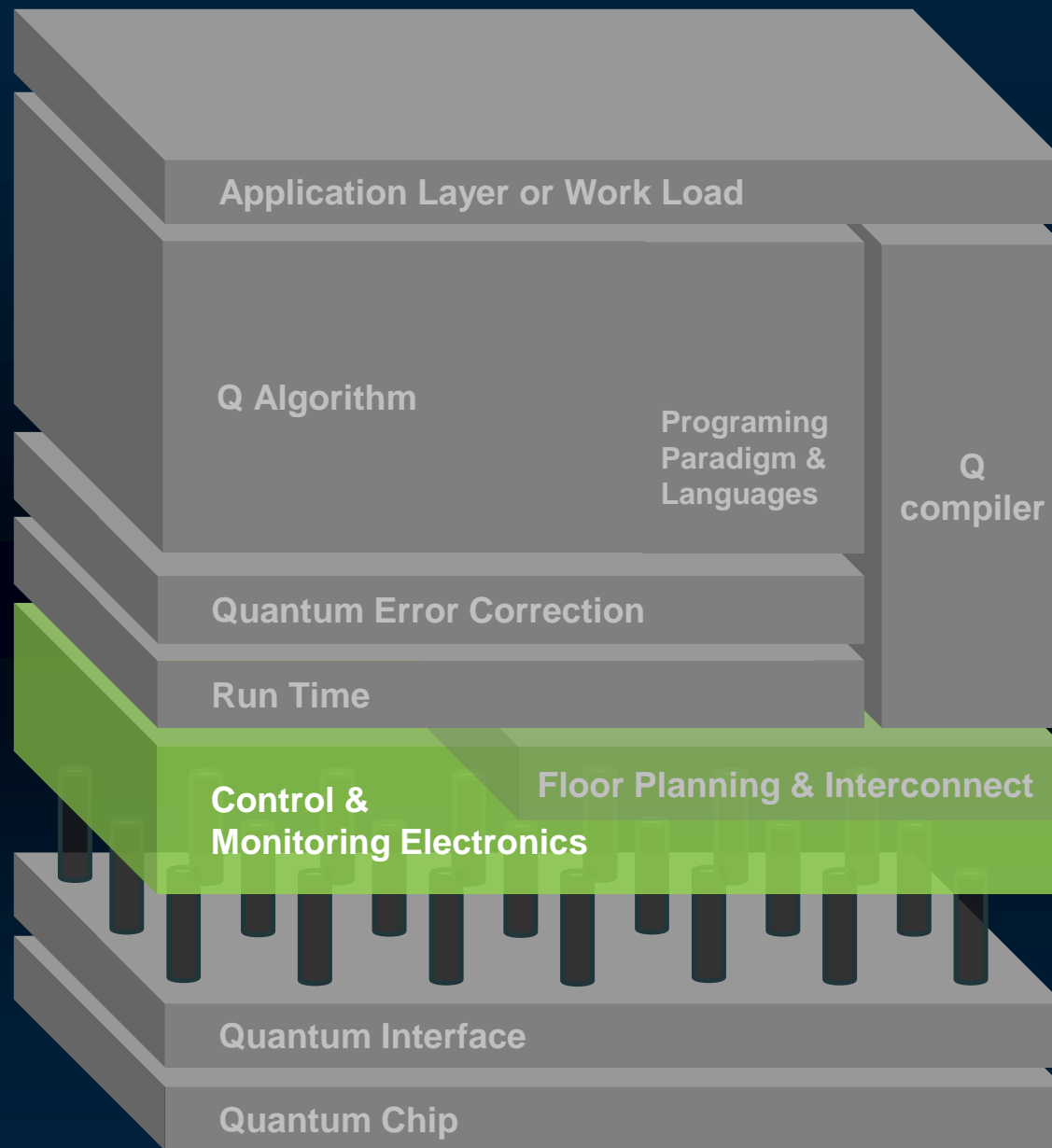
2DEG

FD-SOI back gate moves away from the interfaces

› Charge noise decreases of one order of magnitude



C. Spence and M. Urdampilleta, ArXiv



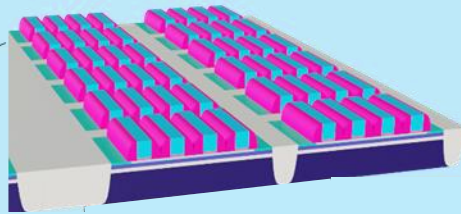
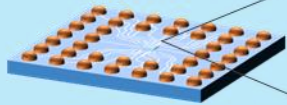
Application Layer or Work Load

300K Control electronics



of wires limits
Thermal dissipation

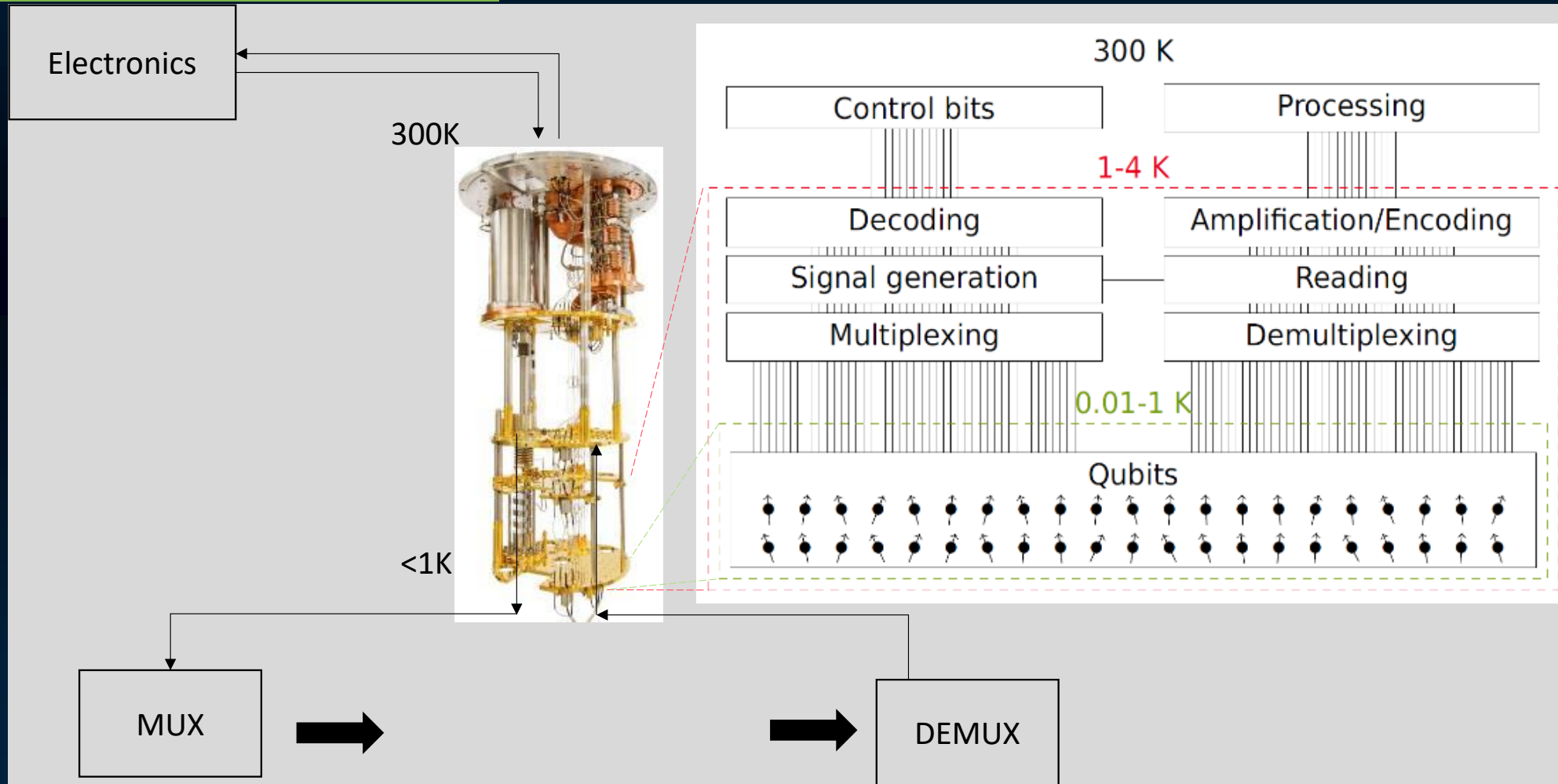
<1K



Qubits array



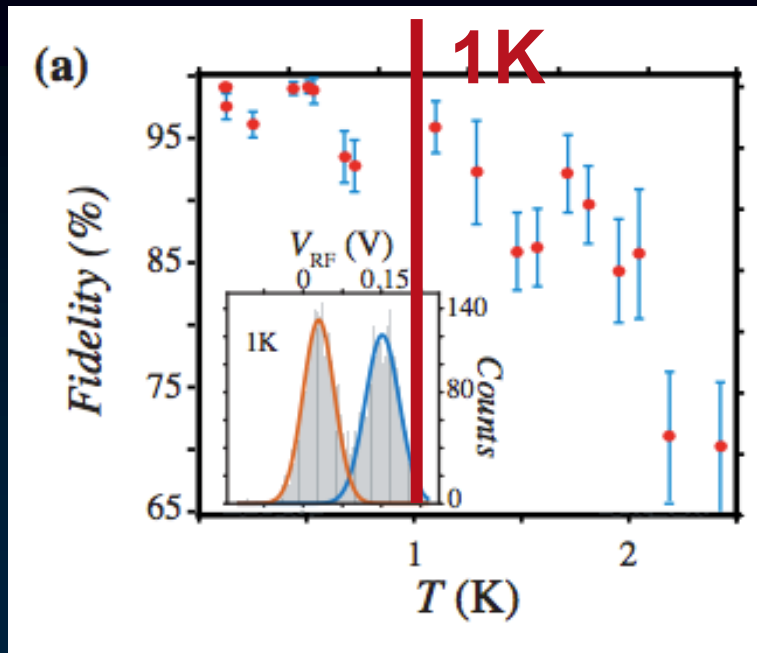
Control & Monitoring Electronics



Control & Monitoring Electronics

T° of operation	Typical cooling power
20mK	30μW
100mK	1mW
1K	100mW-1W

*Urdampilleta et al.,
arXiv:1809.04584*



Dissipated power

=

$$\text{activity} \times \# \text{ of MOS} \times f_{\text{operation}} \times C_{\text{load}} \times V^2$$

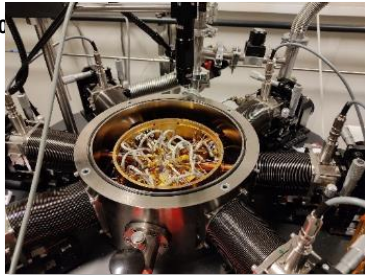
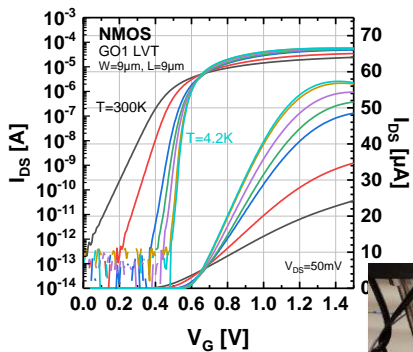
FD-SOI cryogenic control circuits development

Lower power electronics

Paper 34.6 Wednesday @ 4.05pm
M. Cassé, IEDM 2022

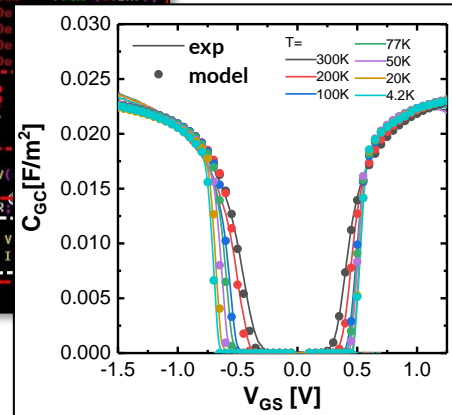
Characterization and modelling

T=300K -100mK

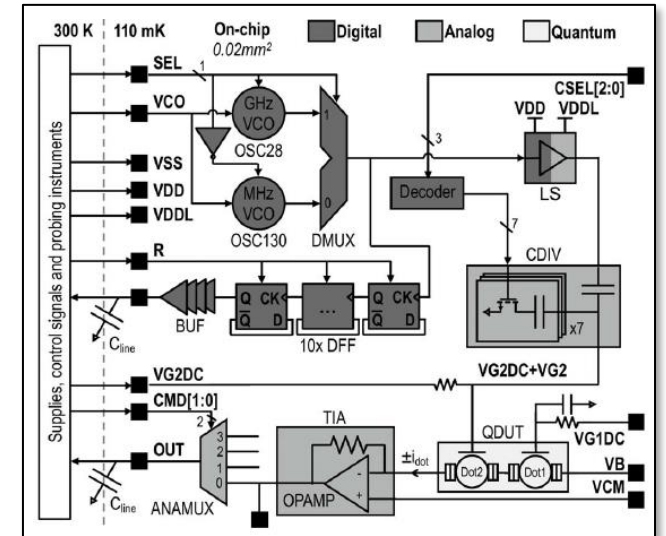


Simulation and CAD tools

```
1 include "disciplines.vams"
2 include "constants.vams"
3
4 module RLcdioIsrc(a, b, c):
5
6   inout a, b, c;
7   electrical a, b, c, i;
8
9   branch (a, i) res, isrc;
10  branch (b, i) cap;
11  branch (c, i) ind;
12  branch (a, b) dio;
13
14  parameter real R = 1.0e3;
15  parameter real L = 1.0e-9;
16  parameter real C = 1.0e-15;
17  parameter real IS = 1.0e-10;
18  parameter real I = 1.0e-10;
19
20  real Id, Vt;
21
22  analog begin
23    Vt <- Vt;
24    Id <- I * exp(Vt / Vt);
25
26    I(res) <- V(res) / R;
27    I(isrc) <- I;
28    I(cap) <- ddt(C * V);
29    V(ind) <- ddt(L * I);
30    I(dio) <- Id;
31
32  end
33 endmodule
```



IC design and test



B. Cardoso Paz et al., VLSI (2020)
M. Cassé et al. Appl. Phys. Lett. (2020)
M. Cassé et al., IntechOpen, (2022)

Back bias

In situ Vt centering

Allows ultra low power RF and digital IC design

FD-SOI as a SoC technology for qubits and control electronics

Successful integration at 1K and tested down to 50mK

- 1 Biasing the two quantum dots from on-chip bias tees,
- 2 Applying GHz mV-level modulation from on-chip frequency- and amplitude-controlled clock generators
- 3 Measuring the induced current through the device from a multiplexed on-chip transimpedance amplifier (TIA).

1 μ W @ 50mK

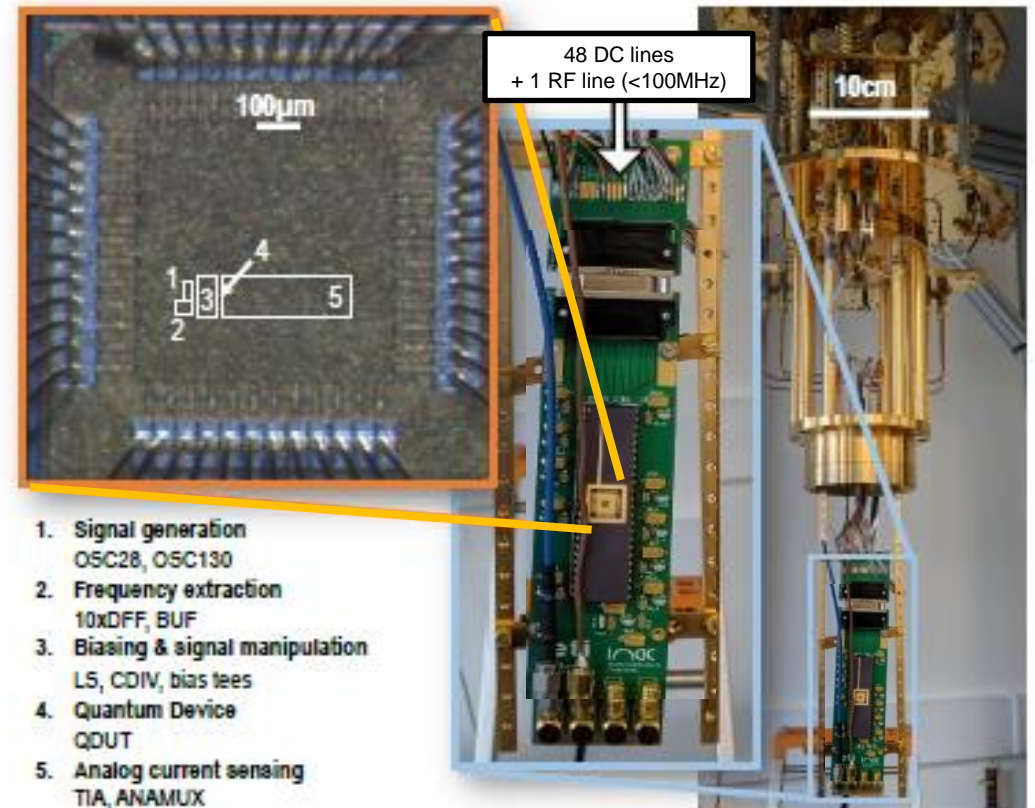


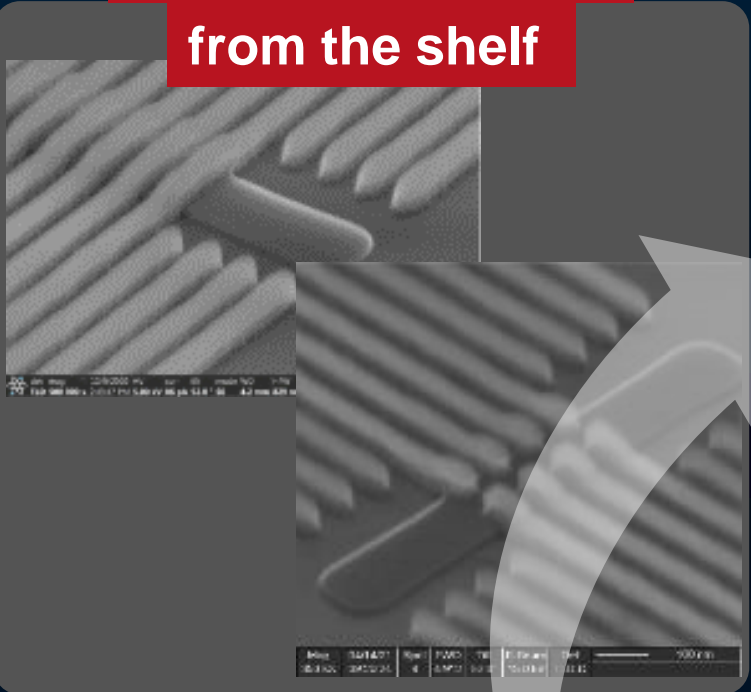
Figure 7: Die micrograph, packaged chip mounting on a PCB with decoupling capacitors, and dilution-fridge mounting.

ISSCC 2020' L. Le Guevel

Applied Phys Rev, L. Le Guevel, 2021

Leveraging VLSI methodology

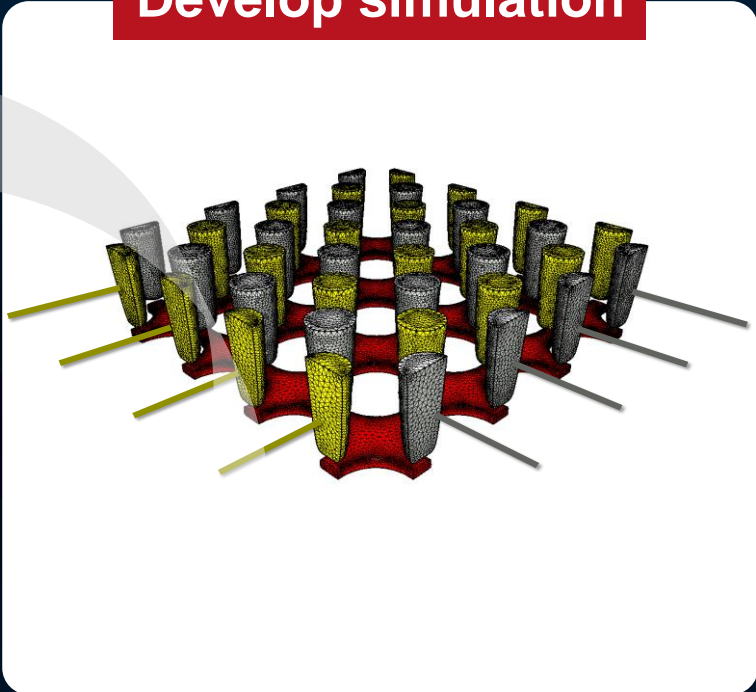
Technology almost from the shelf



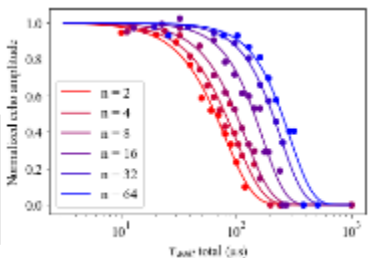
Set up statistical characterization



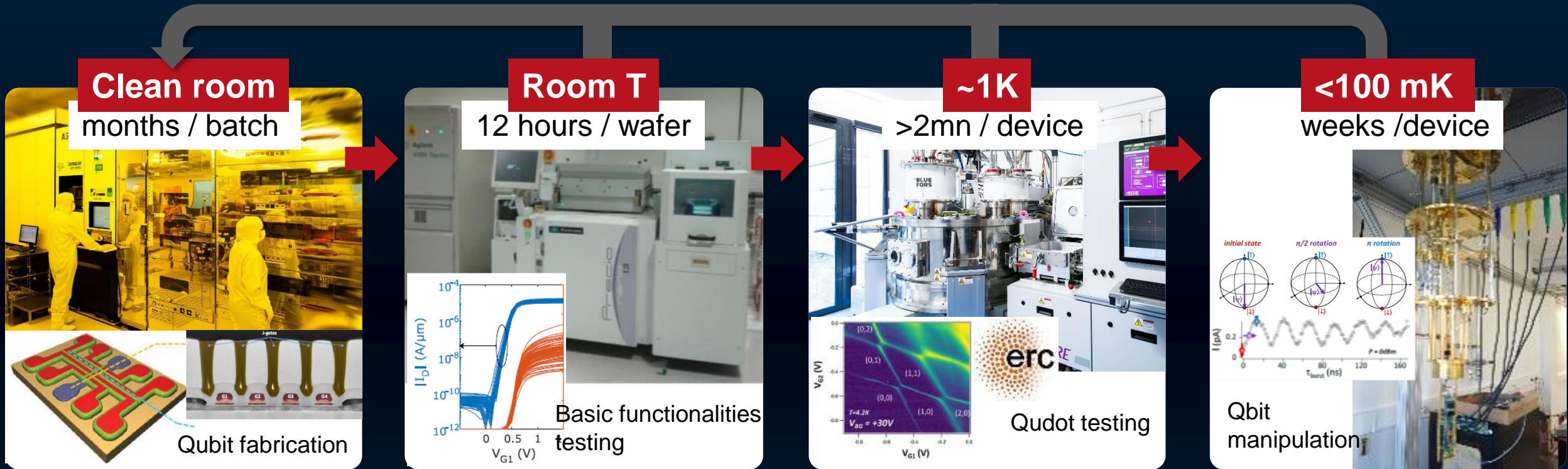
Develop simulation



Physics experiments



From room to low temperature statistical data



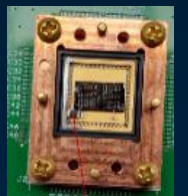
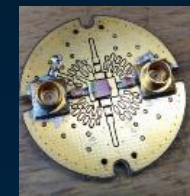
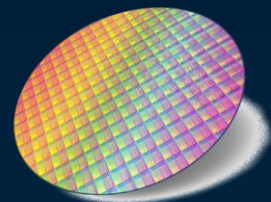
300mm wafer process:
FDSOI CMOS platform

300mm full-wafer prober:
Parametric testers

300mm full-wafer prober:
Bluefors cryoprober

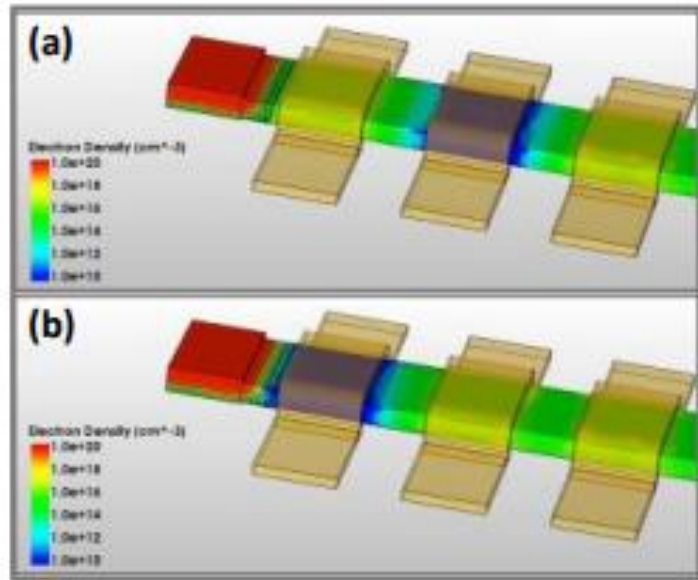
die (<1cm) mounted
on a dilution fridge

\approx 1000 devices
 \sim 100 dies

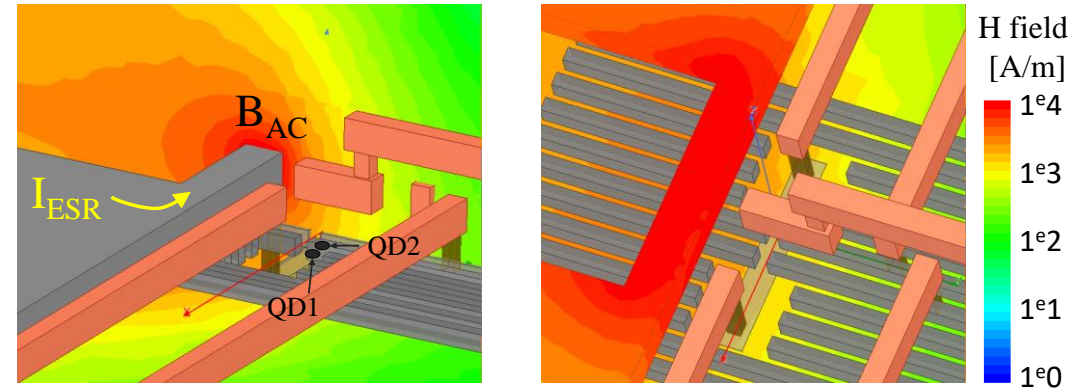


Multi-scale tools for Quantum Computer Aided Design

› Structure & electromagnetism, Classical TCAD



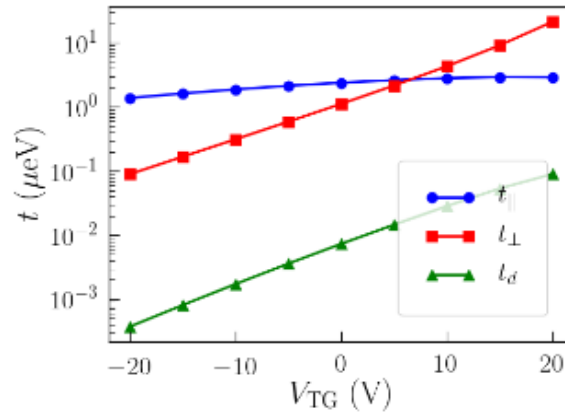
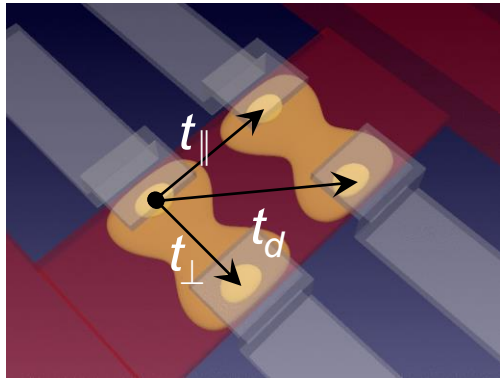
H. Niebojewski, VLSI (2022)



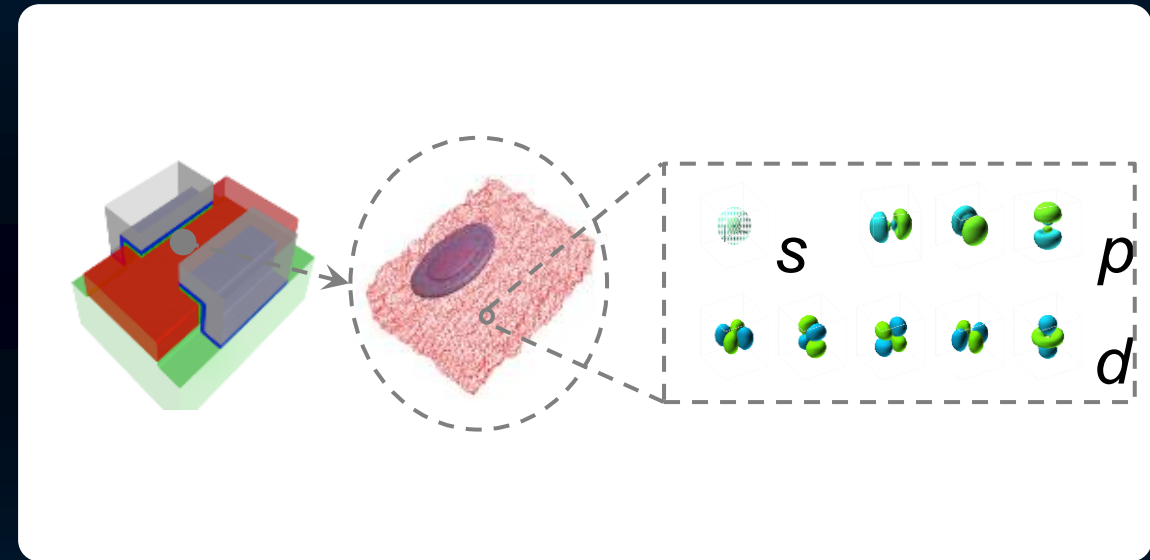
H. Jacquinet SISPAD (2022)
Magnetic field created
by the RF current through an ESR line, used to
manipulate spins

Electronic structure of the dots

- › Finite differences/elements solutions effective mass of of k.p equations
- › Wave functions as linear combination of atomic orbitals



Tunnel couplings between 4 dots wrt the bias on an extra top gate (not shown) at the M1 level



YM Niquet, IEDM 2020 J.Li, B. Venuticci, YM Niquet, unpublished

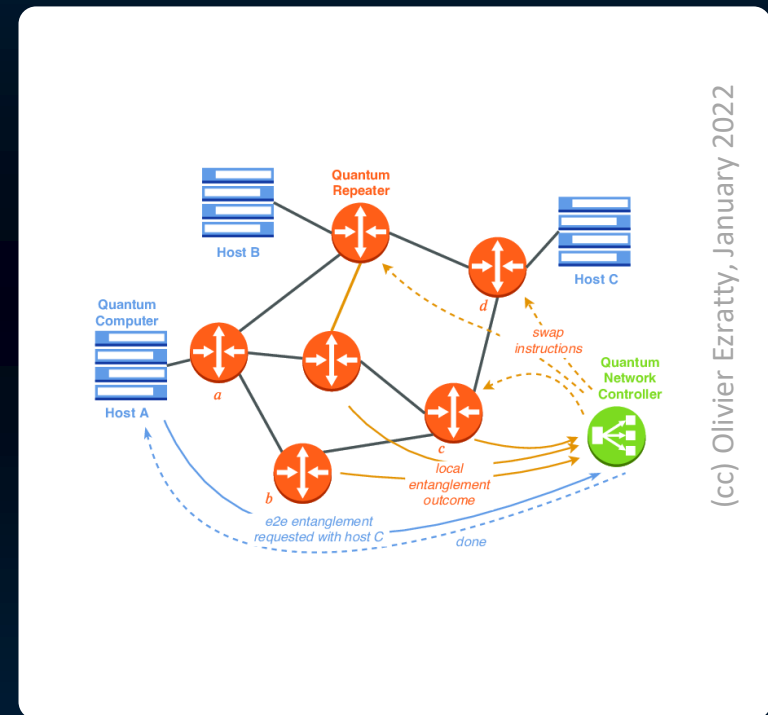
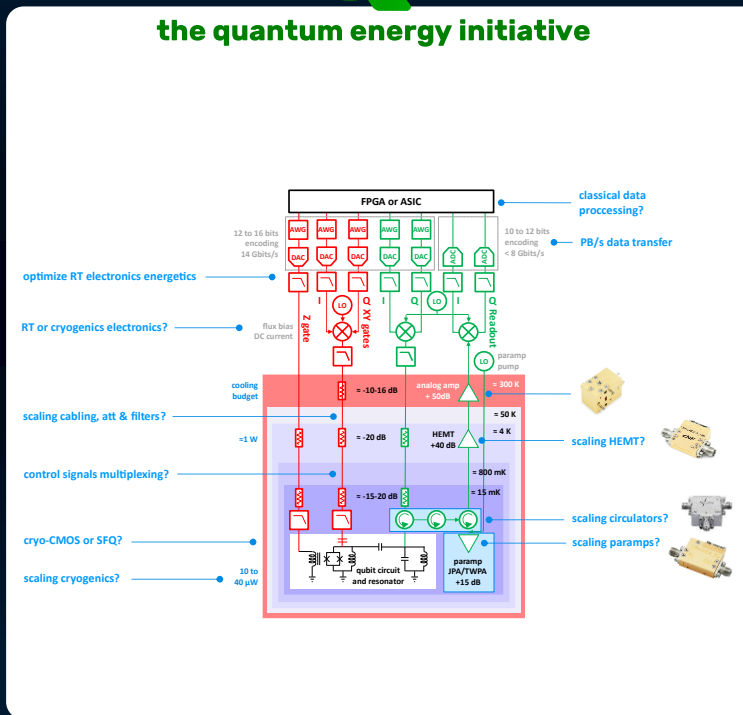
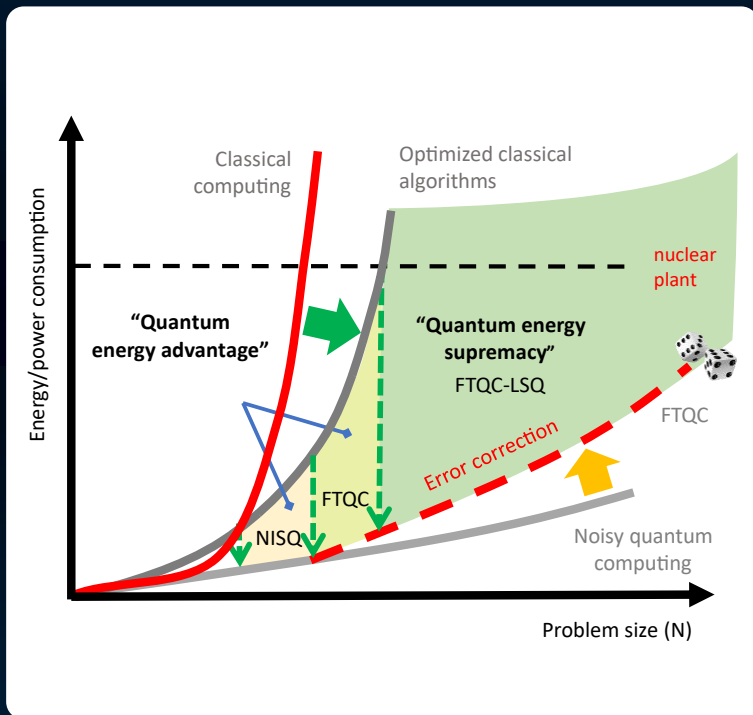
Atomistic modeling of a "corner dot" with surface roughness included

Key scientific questions

- › is there a quantum energy advantage vs classical computing as quantum processors scale up?
- › how different is it from the quantum computational advantage?

#QEI

the quantum energy initiative



(cc) Olivier Ezratty, January 2022

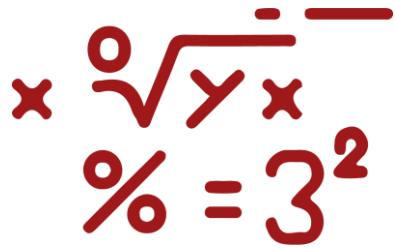
is there a **quantum energy advantage** vs classical computing as quantum processors scale up?
 how different is it from the **quantum computational advantage**?

what is the fundamental **minimal energetic cost** of quantum computing?
 how to **avoid energetic dead-ends** on the road to LSQ?

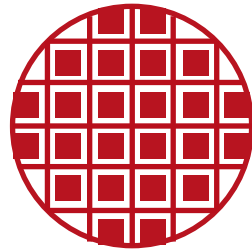
will **other quantum technologies** present energetic challenges?
 quantum communications and sensors

Key messages and perspectives

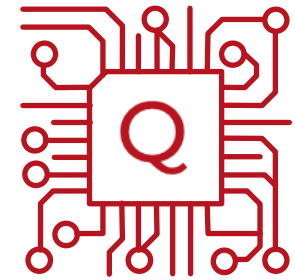
› Turn scientific firsts into reliable quantum processor units



**Quantum computing
has the potential to tackle
untractable problems**



**Silicon provides good qubits
and the semiconductor industry
knows how to fabricate millions
of them**



**Ecosystem and methods are in place
to leverage the potential**

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Silicon based quantum computer



- Spin off from CEA and CNRS, France
- www.siquance.com



Siquance technological roadmap

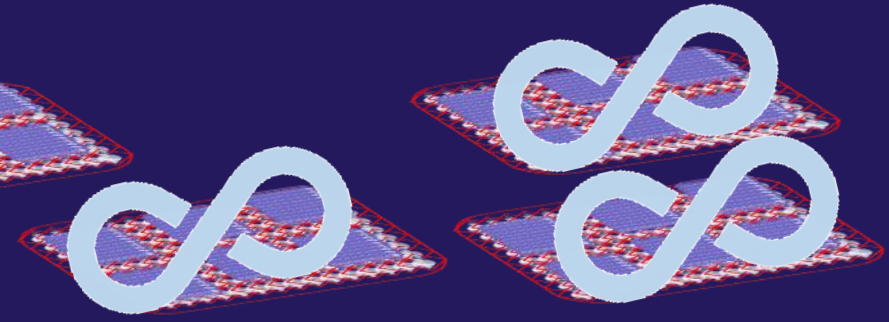
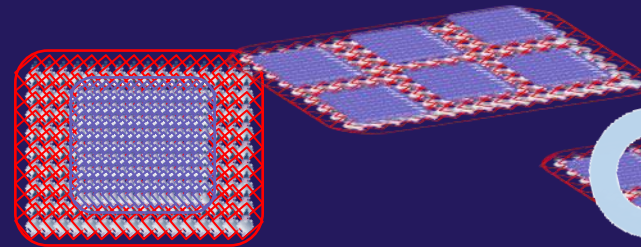
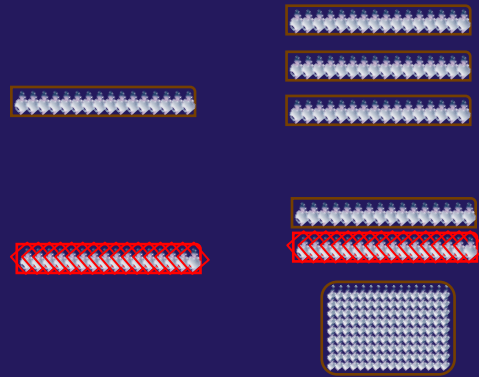
Noisy quantum systems

Quantum advantage PoV

Large scale quantum computing robust to errors

Multi-core 1D quantum processor

Multi-core 2D quantum processor



2022

2030

SoC qubit+cryocontrol
On line cloud access

SoC qubit
array+Cryocontrol

Quantum links

Large scale
quantum
processors



THANK YOU



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